

## Part I

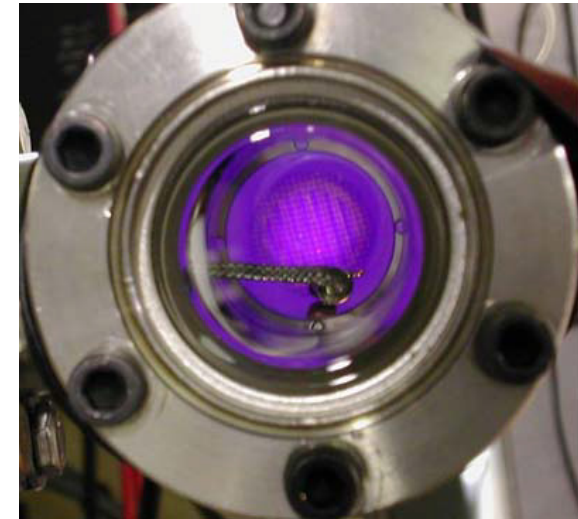
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# Introduction to Electron Sources

T. Thuillier

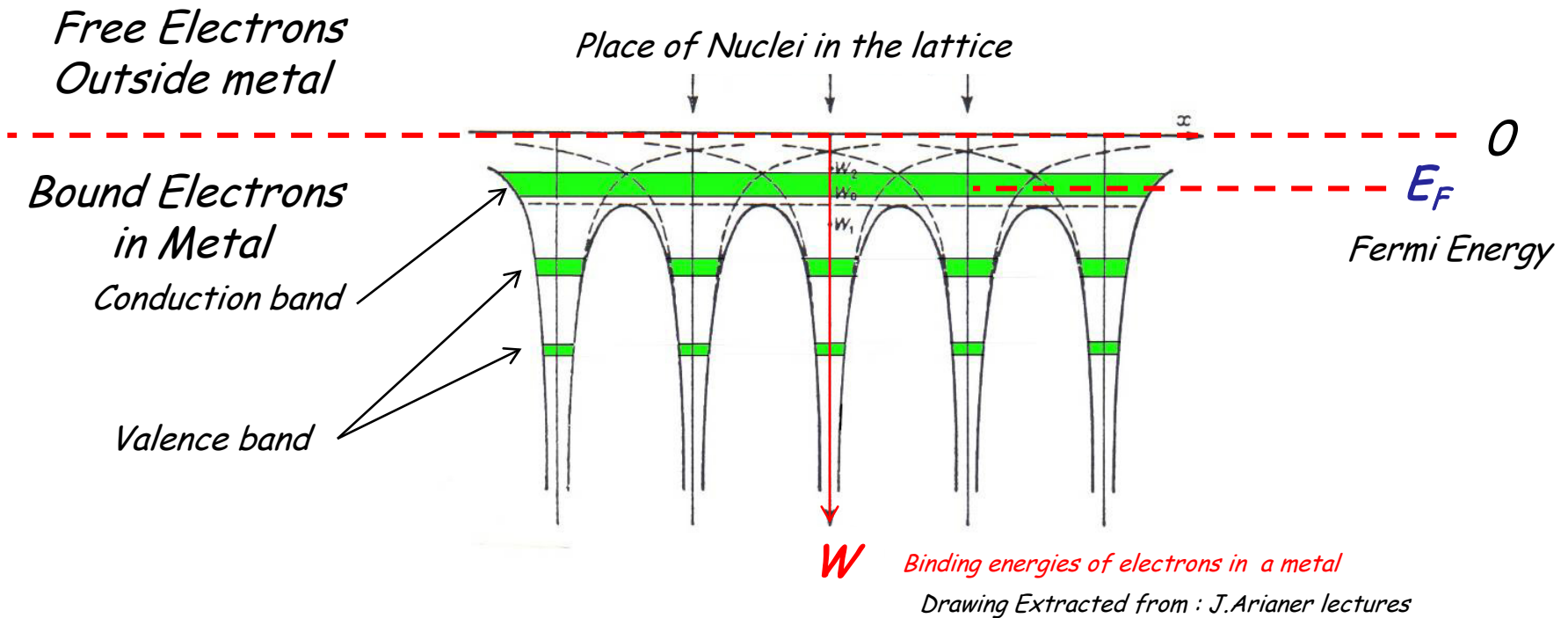
*Laboratoire de Physique Subatomique et de Cosmologie, CNRS -IN2P3-UJF-INPG, 53 rue des martyrs, 38026 GRENOBLE cedex, France*

- Thermionic electron sources
- Field Emission electron sources
- Photo Emission electron sources
- Secondary Emission Electron source
- FerroElectric GUN
- RF GUN



# Work Function of electrons in metals (reminder)

- The **Work Function  $W$**  is the minimum energy needed to remove an electron from a solid to a point immediately outside the solid surface



- In a metal, some electrons are populating the Conduction Band
- The minimum binding energy of electrons in metal corresponds to the Fermi Energy:  $W = E_F$

# Work Function of electrons in metals (wikipedia)

Units: eV electron Volts

reference: CRC handbook on Chemistry and Physics version 2008, p. 12-114.

Note: Work function can change for crystalline elements based upon the orientation.

Element	eV	Element	eV	Element	eV	Element	eV	Element	eV
Ag:	4.52-4.74	Al:	4.06-4.26	As:	3.75	Au:	5.1-5.47	B:	~4.45
Ba:	2.52-2.7	Be:	4.98	Bi:	4.34	C:	~5	Ca:	2.87
Cd:	4.08	Ce:	2.9	Co:	5	Cr:	4.5	Cs:	2.14
Cu:	4.53-5.10	Eu:	2.5	Fe:	4.67-4.81	Ga:	4.32	Gd:	2.90
Hf:	3.9	Hg:	4.475	In:	4.09	Ir:	5.00-5.67	K:	2.29
La:	4	Li:	2.93	Lu:	~3.3	Mg:	3.66	Mn:	4.1
Mo:	4.36-4.95	Na:	2.36	Nb:	3.95-4.87	Nd:	3.2	Ni:	5.04-5.35
Os:	5.93	Pb:	4.25	Pd:	5.22-5.6	Pt:	5.12-5.93	Rb:	2.261
Re:	4.72	Rh:	4.98	Ru:	4.71	Sb:	4.55-4.7	Sc:	3.5
Se:	5.9	Si:	4.60-4.85	Sm:	2.7	Sn:	4.42	Sr:	~2.59
Ta:	4.00-4.80	Tb:	3.00	Te:	4.95	Th:	3.4	Ti:	4.33
Tl:	~3.84	U:	3.63-3.90	V:	4.3	W:	4.32-5.22	Y:	3.1
Yb:	2.60 <sup>[2]</sup>	Zn:	3.63-4.9	Zr:	4.05				

Max

Min

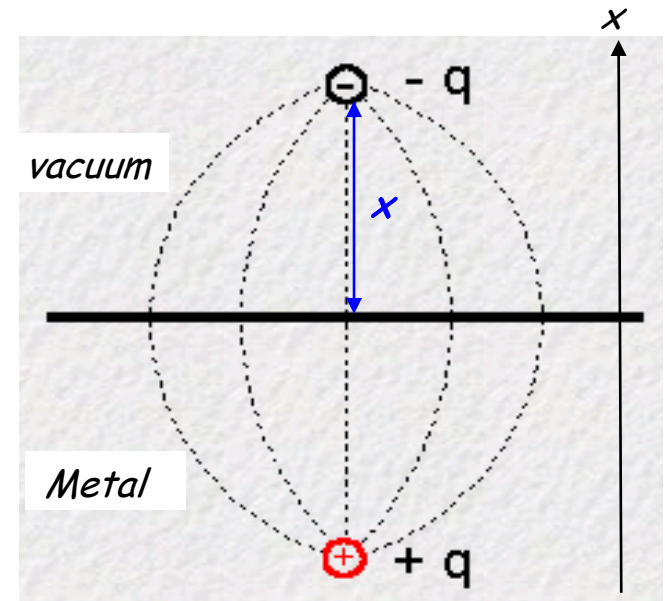
## ➤ The Charge Image

- When an electron ( $-q$  charge) is extracted from a metal, a  $+q$  image charge (hole) is created in the metal that screens exactly the electric field generated by the electron at the metal surface (at  $x=0$ )
- The Electric Field  $E(x)$  generated by the charge image (hole) acting on the electron is:

$$E(x) = \frac{+q}{4\pi\epsilon_0} \frac{1}{(2x)^2}$$

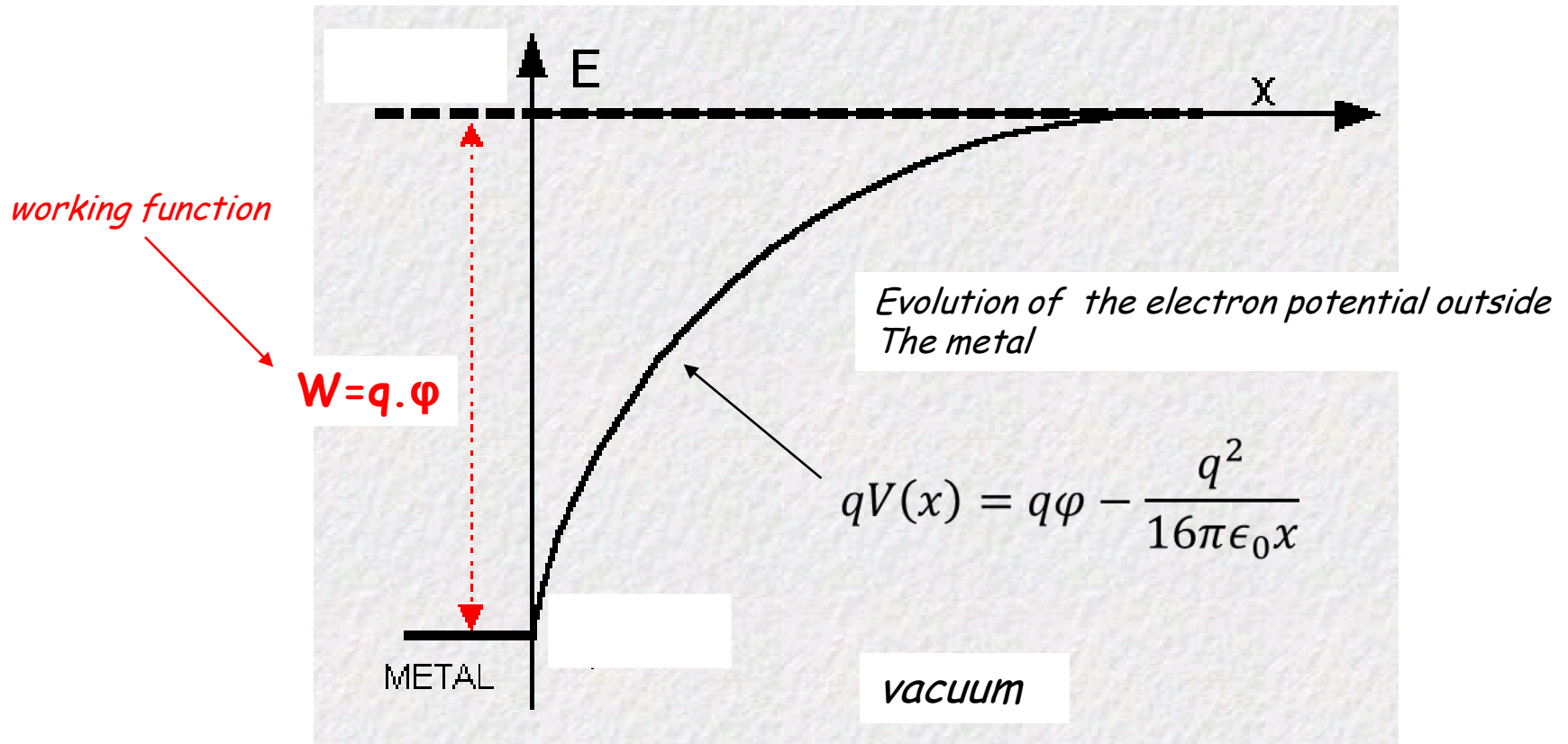
- This electric field tends to attract back the electron toward the metal
- The Associated potential energy  $V_{CI}(x)$  is:

$$V_{CI}(x) = -\frac{q}{16\pi\epsilon_0} \frac{1}{x}$$



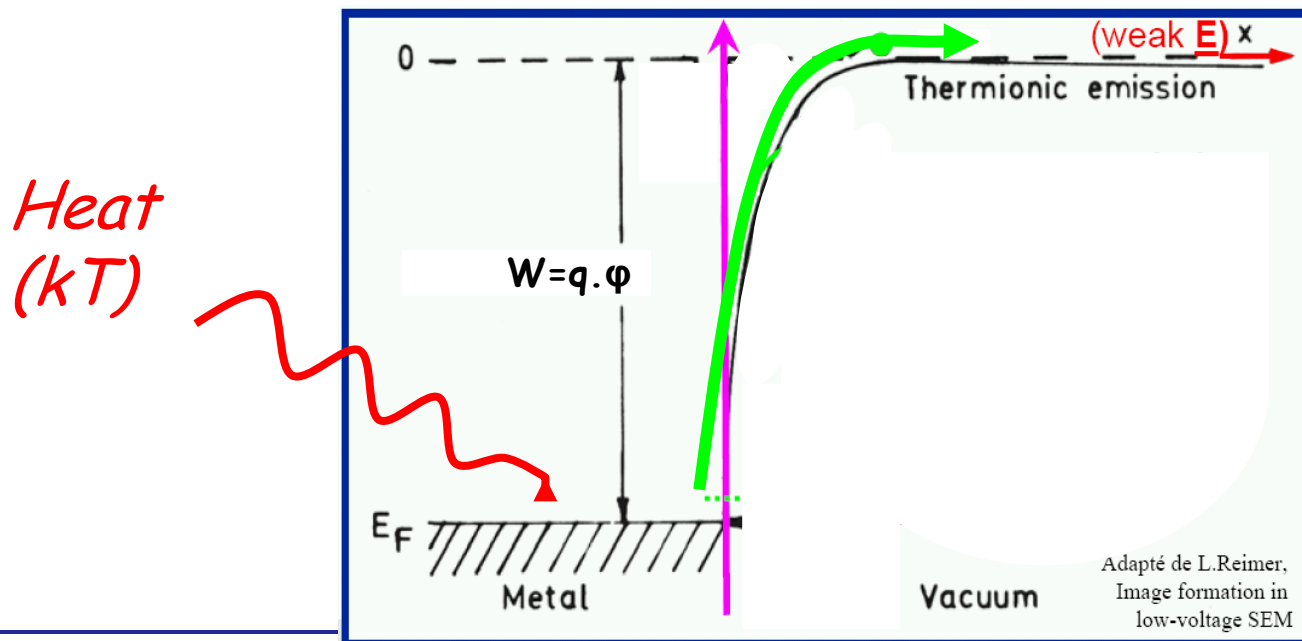
## Dipole effect near to a Metallic Surface (2/2)

- Resulting potential plot near to a metallic surface due to the charge image is  $V(x)=W-V_{CI}(x)$
- The electron should be extracted with an energy  $E>W=q.\phi$



# Thermionic Emission of electrons (1/3)

- The first way to extract electrons is to heat the metal to high temperature  $T$ 
  - When the metal is heated, the thermal vibrational energy of electrons can exceed the Work Function :  $kT > e \cdot \phi$
- **The thermionic emission** is the resulting flow of electrons extracted from the heated metal
- Application of a negative voltage (**weak E field**) helps electron extraction from the metal surface



# Current density from Thermionic Emission (1/3)

The Thermionic emission flow is ruled by the Richardson-Dushman equation

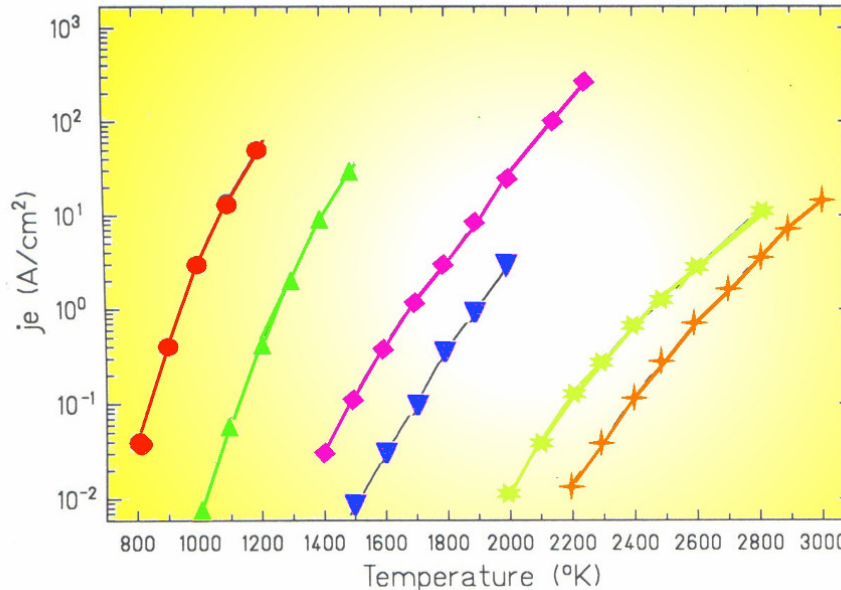
- $J$  current density (A/cm<sup>2</sup>)
- $A$  Richardson constant
- $W = q \cdot \phi$  work function

$$J = AT^2 e^{\frac{-W}{kT}}$$

$$A = \frac{4\pi mk^2 e}{h^3} = 1.20173 \times 10^6 \text{ A m}^{-2}$$

Order of magnitudes :

- **W**olfram :  $W_w \sim 4.5 \text{ eV}$  ;  $T_w \sim 2700 \text{ K}$  →  $J \sim 10 \text{ A/cm}^2$
- **LaB<sub>6</sub>** :  $W_{LaB_6} \sim 2.4 \text{ eV}$  ;  $T_{LaB_6} \sim 2100 \text{ K}$  →  $J \sim 10^2 \text{ A/cm}^2$



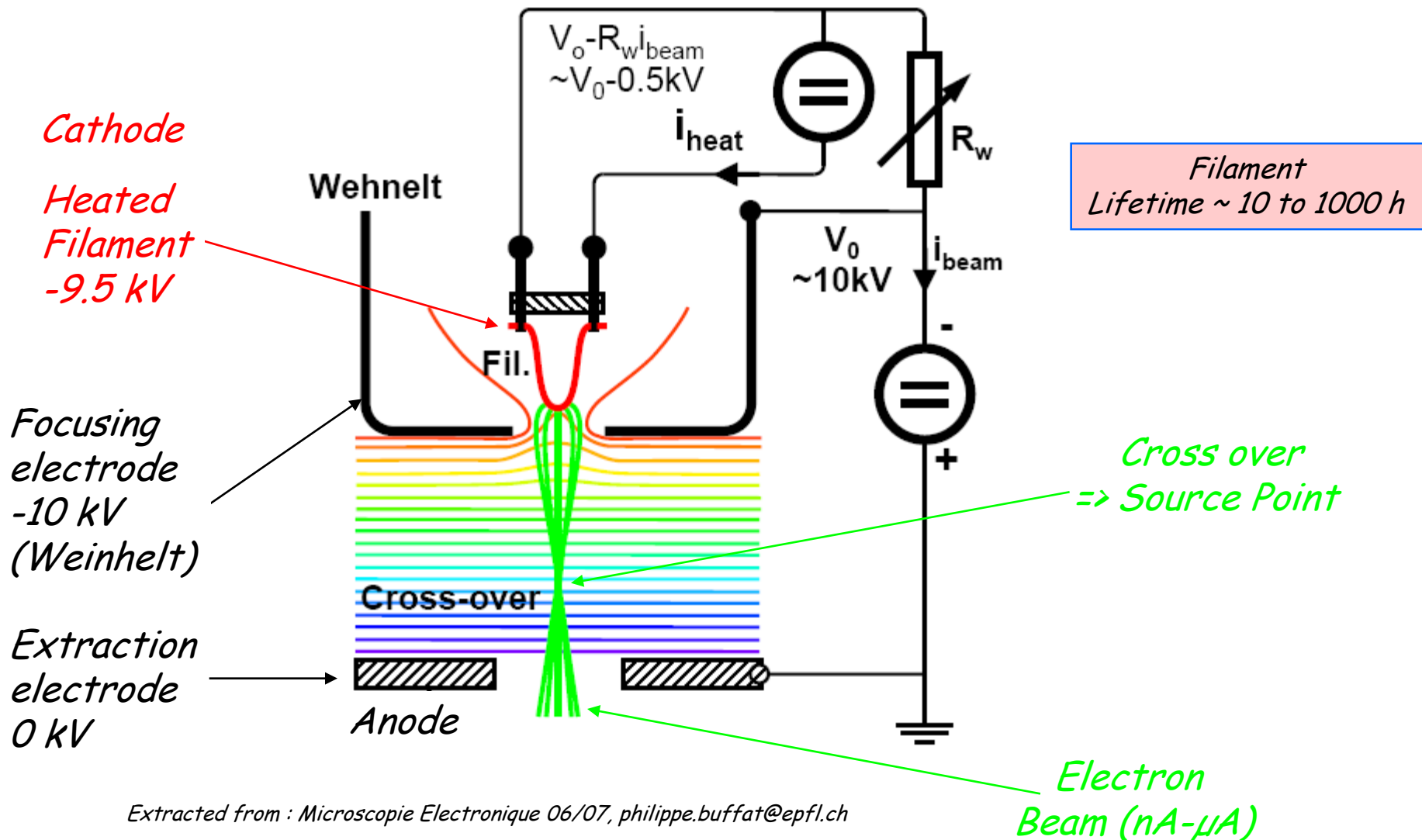
- BaOSrO ← BaO=1.57 eV
- ▲ Ba on W
- ◆ LaB<sub>6</sub> ← LaB<sub>6</sub>=2.66 eV
- ▼ Th on W
- ★ Ta
- ✦ W ← W= 4.53 eV

Extracted from : J.Arianer lectures



# Example of a Thermionic Electron Gun

## Electronic Microscope source





# High intensity Thermionic Electron gun

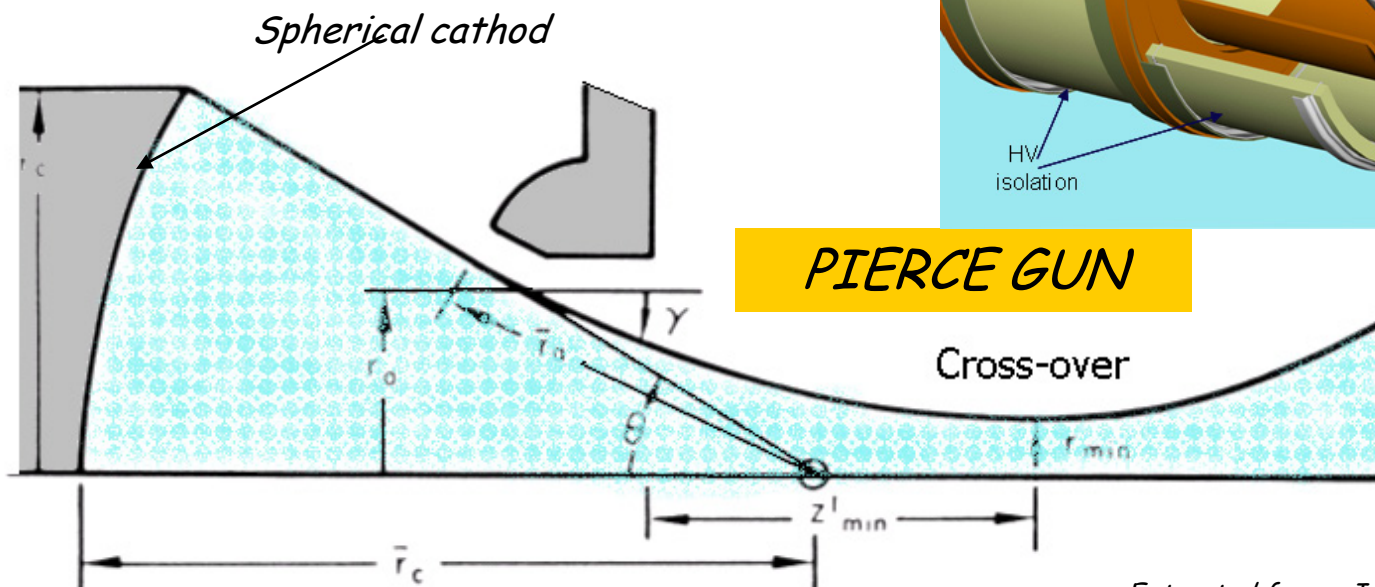
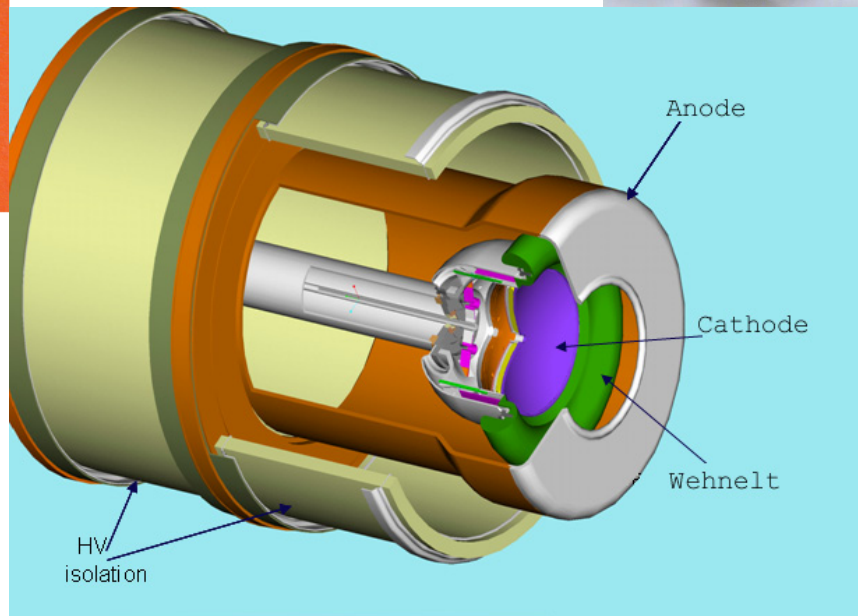
Depending on the design:  
Currents from  $\mu A$  to  $\sim 100 A$



Example of cathodes



cathodes damaged by sputtering (see later)



Extracted from : J.Arianer lectures

# The Schottky Effect (1/2)

➤ Schottky effect : reduction of the electron work function when an external electric field  $E$  is applied

- Potential energy for  $E$ :  $V(x) = -E \cdot x$
- New total potential  $V_S(x)$ :

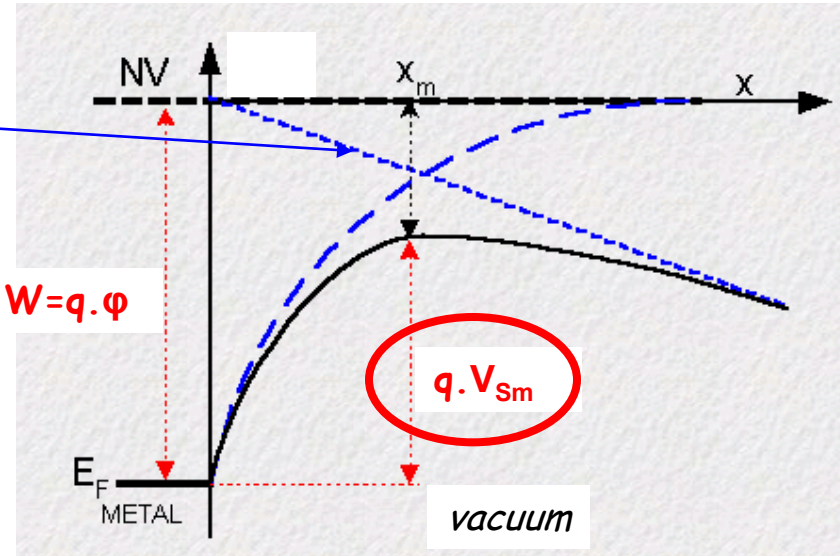
$$qV_S(x) = q\phi - \frac{q^2}{16\pi\epsilon_0 x} - qE \cdot x$$

- Location of the optimum in  $x_m$ :

$$x_m = \sqrt{\frac{q}{16\pi\epsilon_0 E}}$$

- And the reduced working function  $qV_{Sm}$  is:

$$qV_{Sm} = q\phi - \delta W \quad \text{with} \quad \delta W = 2qE \cdot x_m = \sqrt{\frac{q^3 E}{4\pi\epsilon_0}}$$



➤ Schottky effect is usually of second order :

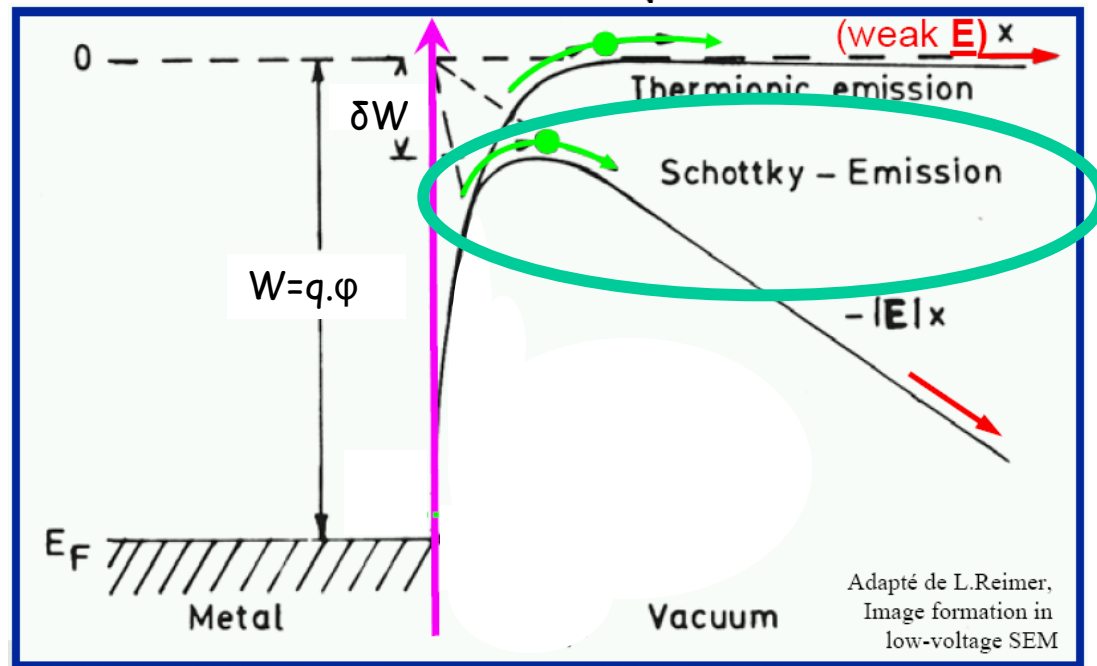
- $E = 10 \text{ kV/cm} \Rightarrow \delta W = 30 \text{ meV}$
- $E = 100 \text{ kV/cm} \Rightarrow \delta W = 100 \text{ meV}$
- Effect valid up to  $E \sim 1 \text{ MV/cm} \Rightarrow \delta W = 0,3 \text{ eV}$

# Schottky Emission of Electrons (2/2)

- Corrected Richardson-Dushman equation in presence of an externally applied medium electric field (Schottky emission)
- The Thermionic emission is enhanced thanks to the Work function decrease  $\delta W$

$$J(E, T, W) = AT^2 e^{\frac{-(W-\delta W)}{kT}}$$

$$\delta W = \sqrt{\frac{q^3 E}{4\pi\epsilon_0}}$$

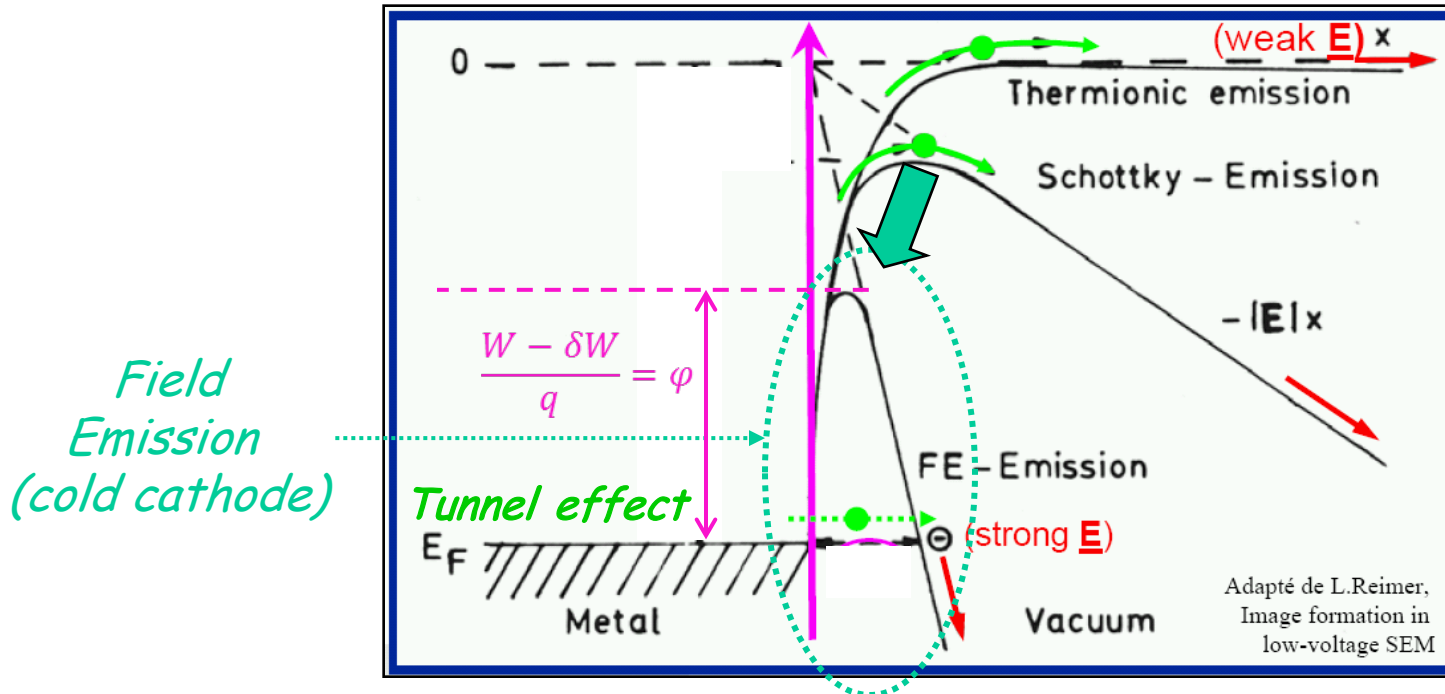


# Field Electron Emission

- In the presence of a very **strong electric field** ( $E \sim 10 \text{ MV/cm}$ ), the working barrier is thin enough to allow electron emission through Tunnel Effect
- The associated emission is ruled by the Fowler-Nordheim theory
- It is a cold cathode emission  $\Rightarrow$  no metal heating is required

$$J \approx \frac{k_1 E^2}{\varphi} e^{-\left(\frac{k_2 \varphi^{3/2}}{E}\right)} \quad \begin{array}{l} k_1 = 1.4 \cdot 10^{-6} \text{ (SI)} \\ k_2 = 6.87 \cdot 10^7 \text{ (SI)} \end{array}$$

- $J \sim 10^6 \text{ A/cm}^2$

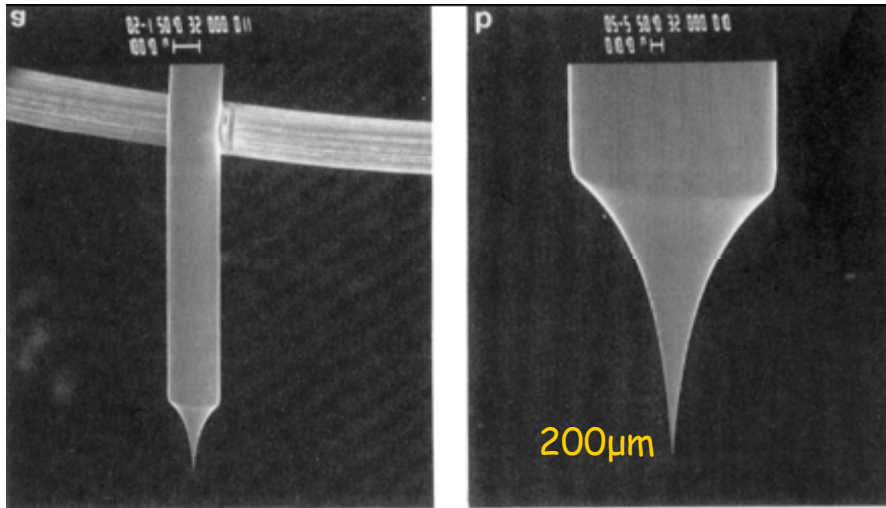


Adapted from :  
Microscopie Electronique 06/07,  
philippe.buffat@epfl.ch



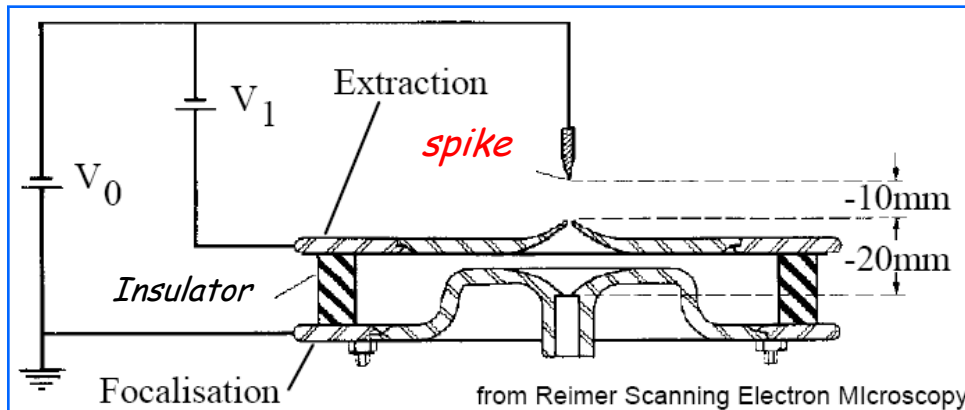
# Field Emission Electron Source (electronic microscopy)

Example of a spike that concentrates the Electric field



The lower the radius of the tip, the higher the electric field

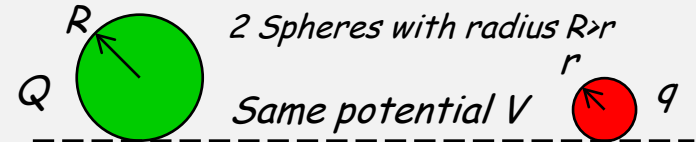
(from J. Goldstein, Scanning electron microscopy)



from Reimer Scanning Electron Microscopy

Extracted from : Microscopie Electronique 06/07, philippe.buffat@epfl.ch

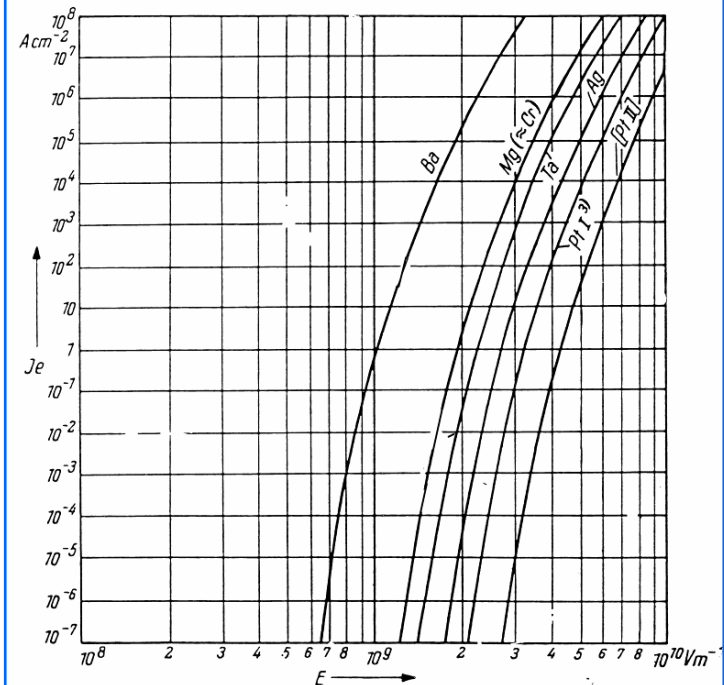
## Electrostatic Point effect (Corona)



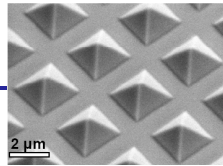
$$V = \frac{Q}{4\pi\epsilon_0 R} = \frac{q}{4\pi\epsilon_0 r} \quad \text{at spheres surface}$$

$$E_1(R) = \frac{Q}{4\pi\epsilon_0 R^2} \quad E_2(r) = \frac{q}{4\pi\epsilon_0 r^2}$$

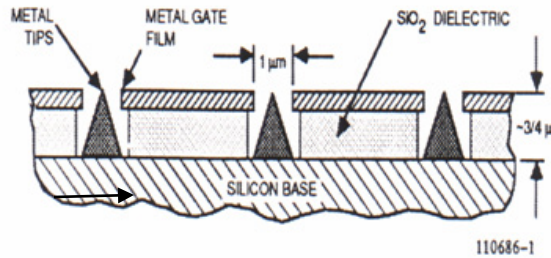
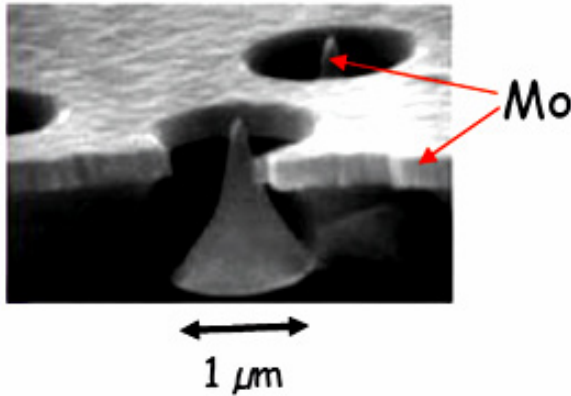
$$\Rightarrow E_2(r) = E_1(R) \cdot \frac{R}{r}$$



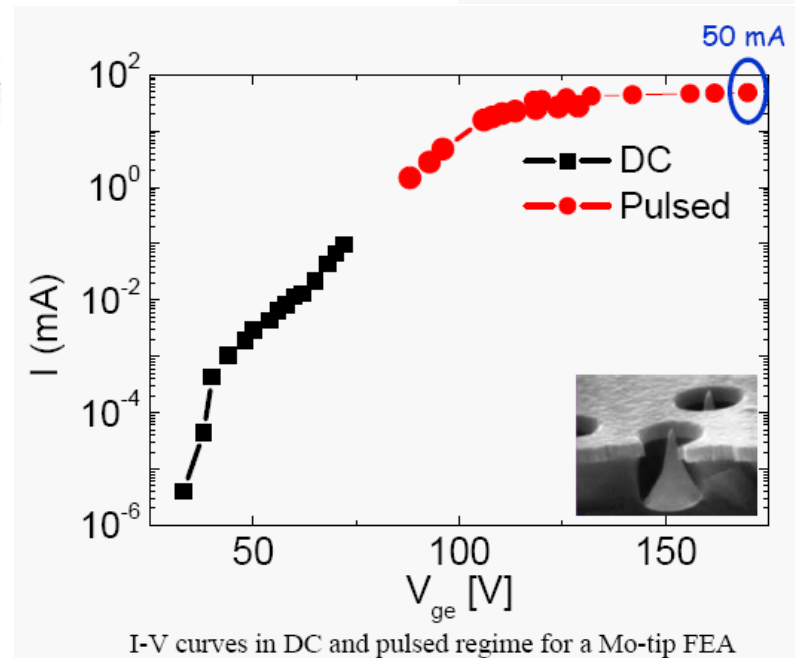
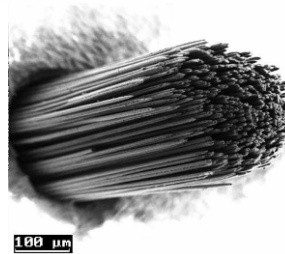
# Field Emission Array GUN



- Built on Si base substrate, using semi-conductor technology
  - Generation of large surface of Field emission array
  - At PSI: 50000 Mo spikes (tips) on a Ø 1 mm disk
  - Requires ultra high vacuum level



PSI

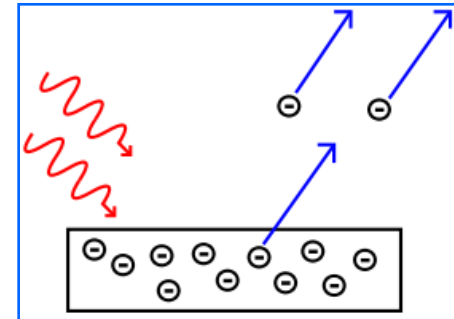


Extracted from : J.Arianer lectures

# Photoelectric Effect

➤ The energy to emit an electron is given by a photon

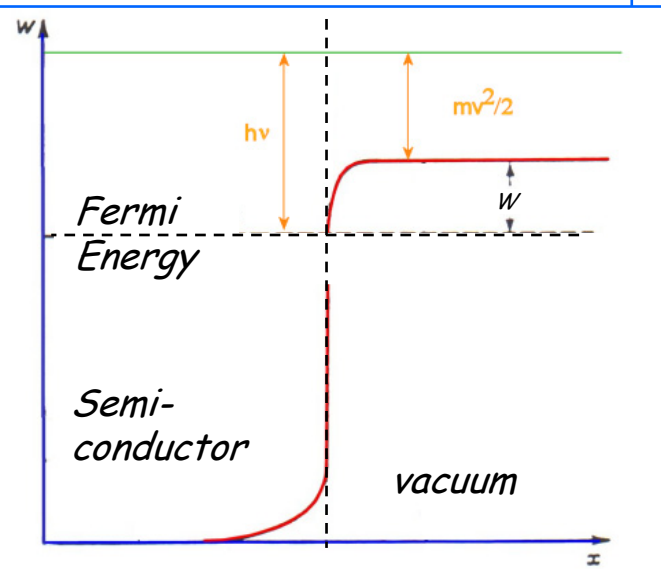
- A photocathode is a negatively charged electrode coated with a photosensitive compound. When it is struck by a photon, the absorbed energy causes electron emission due to the photoelectric effect.
- A photocathode is usually composed of alkali metals with very low work functions (e.g. Cesium).



$$h\nu = W + \frac{1}{2}mv^2$$

$W = \text{Work function of photocathode}$

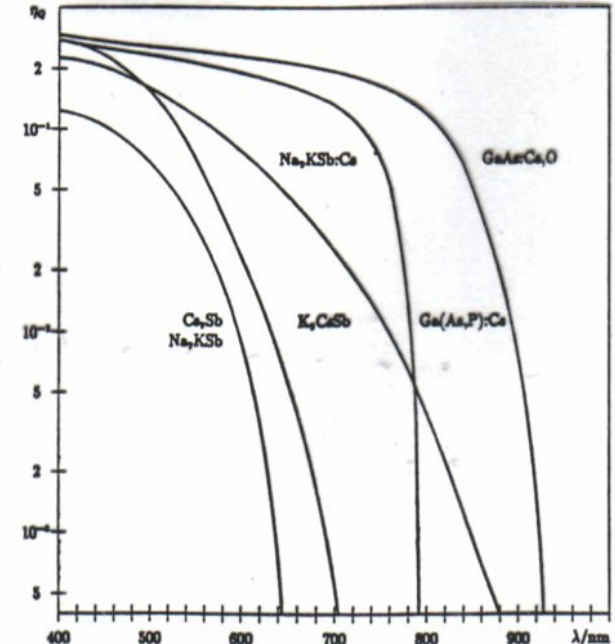
*Photon energy*      *Electron kinetic energy*



$$\lambda_{[nm]} = \frac{1234}{W_{[eV]}}$$

Material	$\Delta E$ [eV]	$\lambda_0$ [nm]
Cs <sub>3</sub> Sb	1.95	640
K <sub>2</sub> CsSb	1.8	700
Na <sub>2</sub> KSb:Cs	1.4	890
GaAs:Cs <sub>2</sub> O	1.35	930

*Photocathodes  
Quantum efficiencies  
(semi conductors)*



Extracted from : J.Arianer lectures

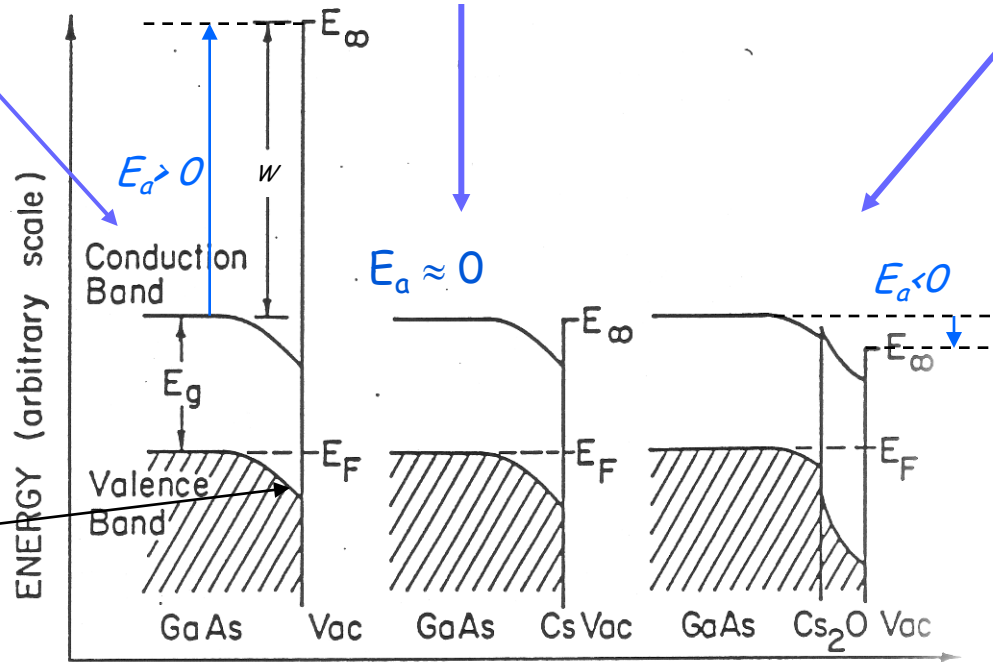
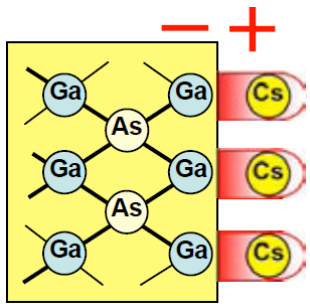


# Photoemission Enhancement from GaAs with Cs or Cs-X coating

Bare GaAs surface;  
Large work function.  
No electrons

Alkali (Cs) coating  
reduces work function.  
Some electrons.

Cesium + Oxidant (O or NF<sub>3</sub>)  
"Negative Electron Affinity".  
Many electrons



Band bending\*\*

Coating is Very fragile.  
Any chemical contamination  
can damage it.  
=> Excellent ultra high  
vacuum level is necessary

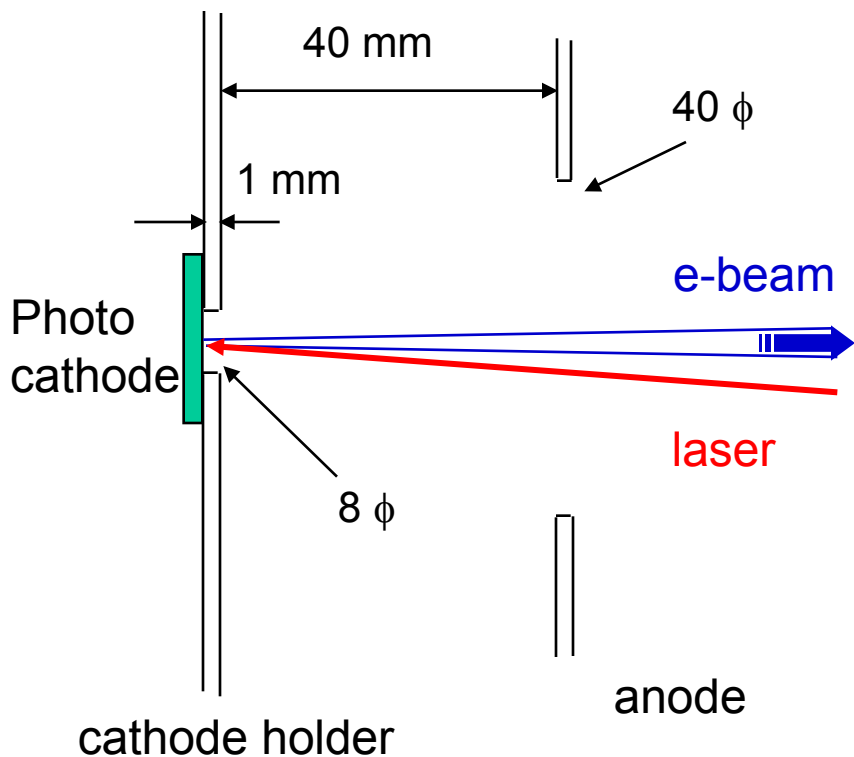
Electron Affinity\* :  $E_a > 0$      $E_a \approx 0$      $E_a < 0$

Extracted from slides :  
J. Grames, JLab, USA  
N. Nishimori, JAEA, Japan

\*In solids, the *Electron Affinity* is the energy difference between the vacuum energy and the conduction band minimum.

\*\*Band bending refers to the local change in energy of electrons at a semiconductor junction due to space charge effects. The degree of band bending between two layers depends on the relative Fermi levels and carrier concentrations of the materials forming the junction.

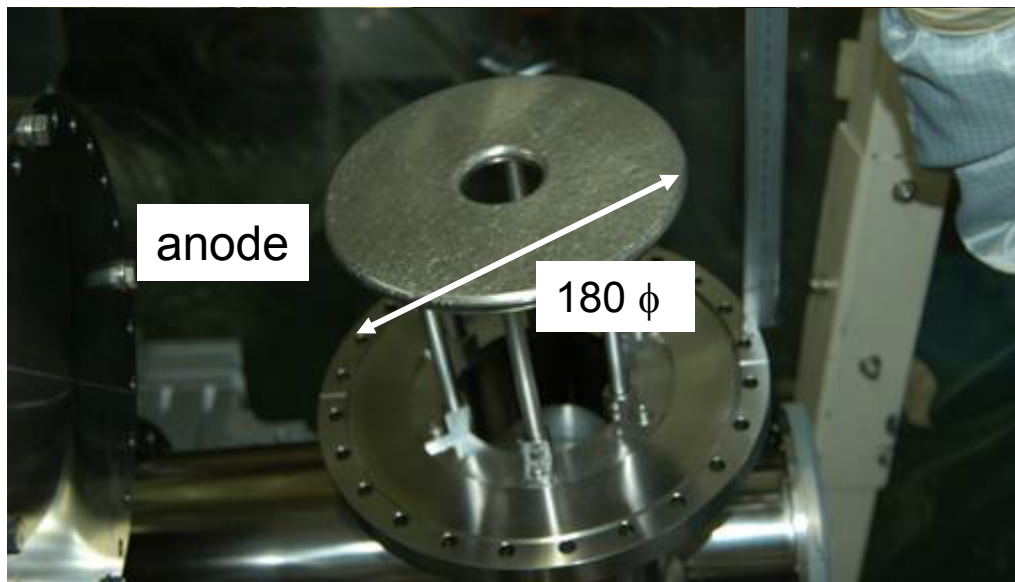
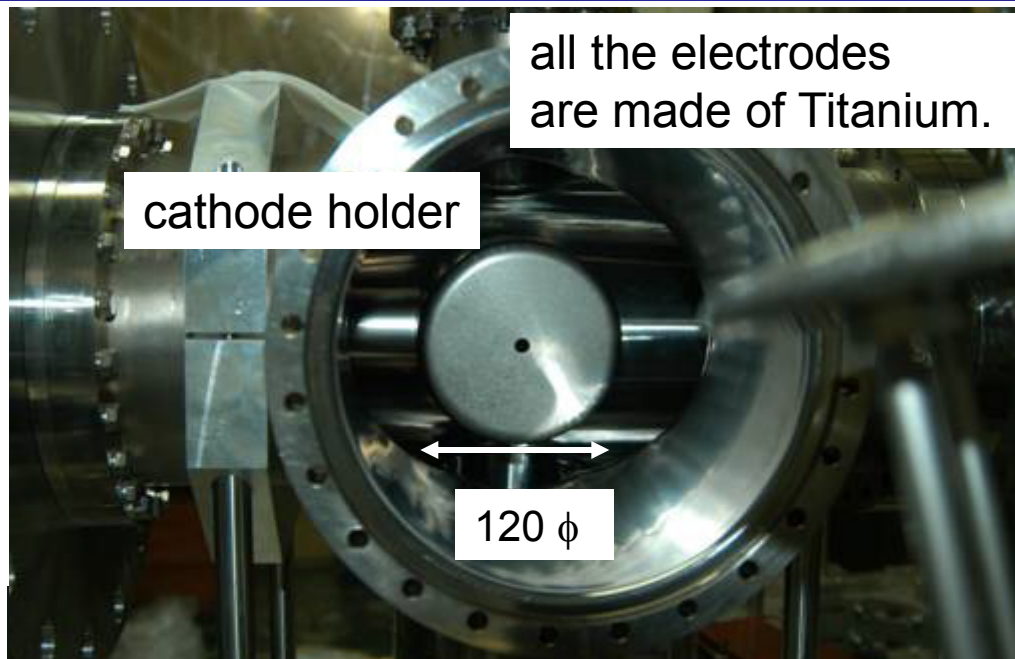
# Example of a Photocathode DC GUN (JAEA-ERL)



The electric field is 5 MV/m.

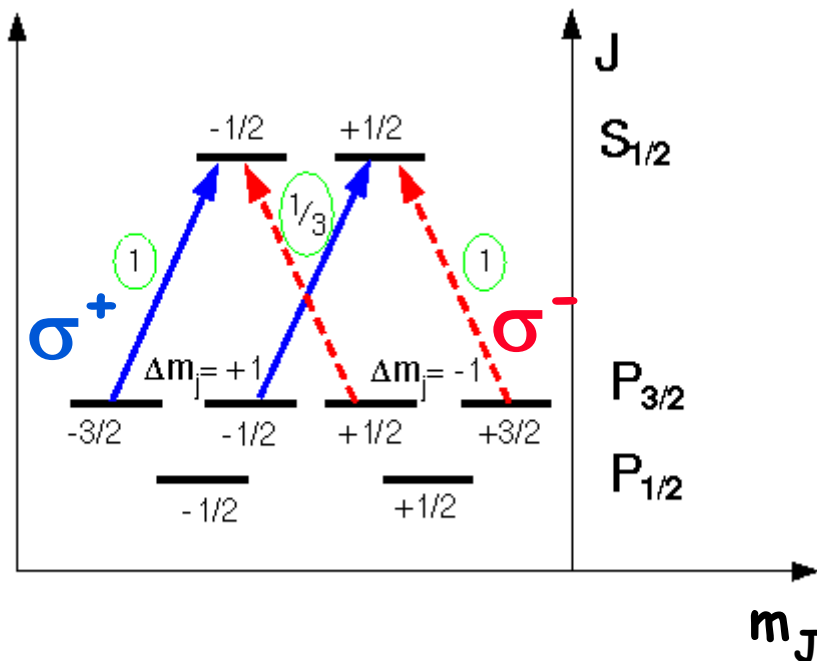
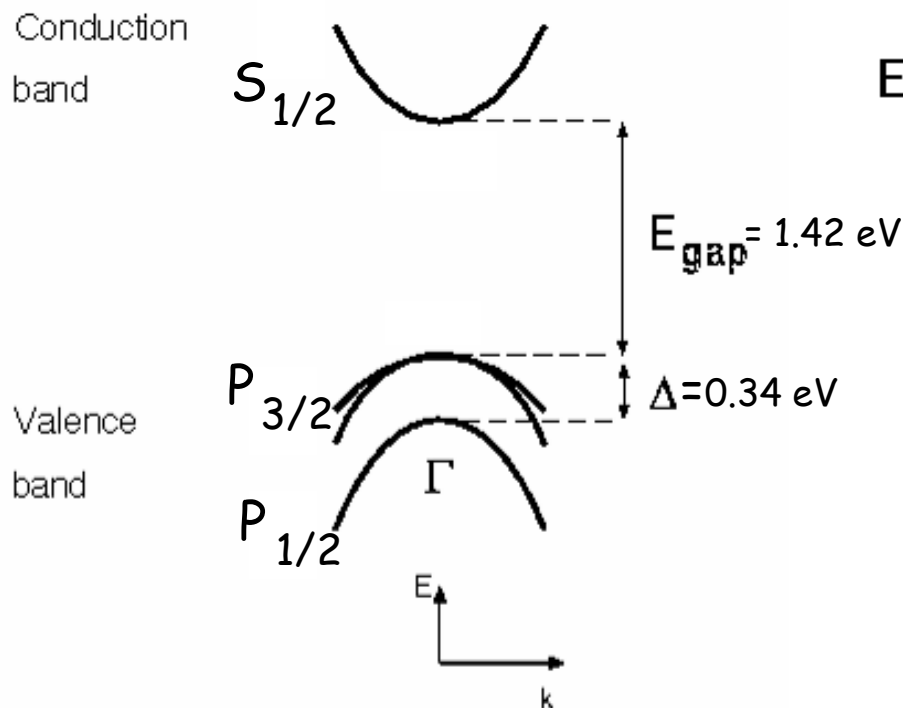
*Goal is 50 mA DC beam*

*Slide is from : N. Nishimori, JAEA, Japan*



# Optical pumping between $P_{3/2}$ and $S_{1/2}$

Circularly polarized Laser :  $\sigma^+$  or  $\sigma^-$



Photon energy

$$E_{\text{gap}} < E_{\gamma} < E_{\text{gap} + \Delta}$$

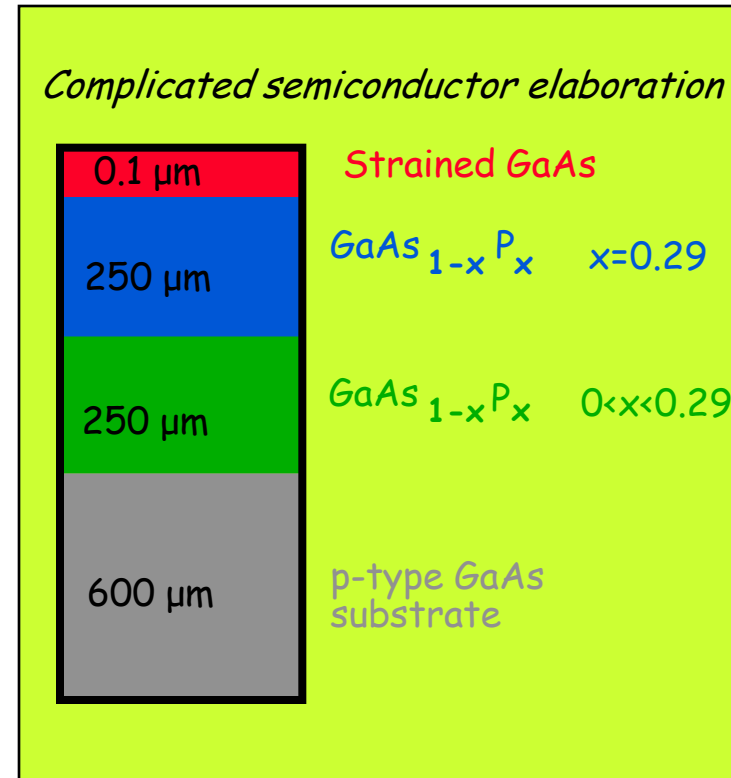
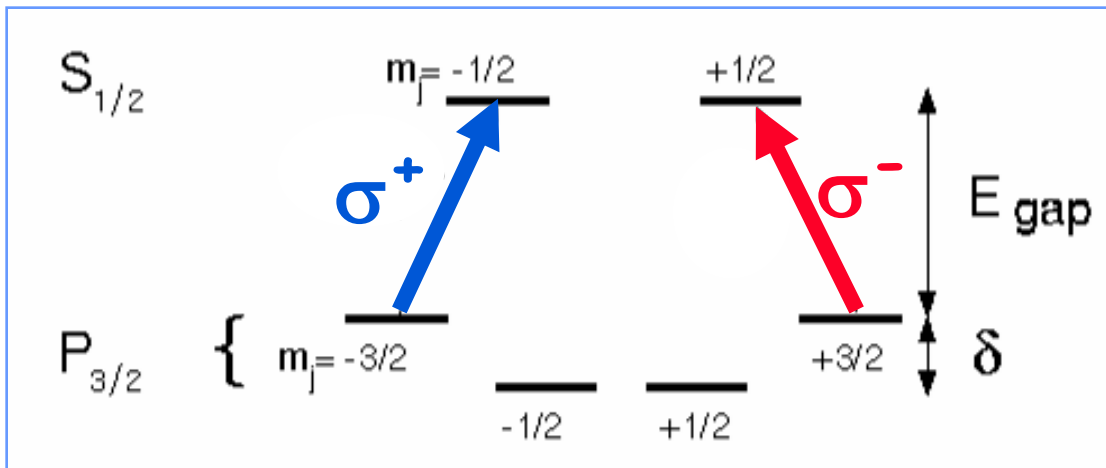
$hc / \lambda$

(excess of...) Polarization Ratio of the electron beam

$$P_e = \frac{3-1}{3+1} = +/- 50\%$$

# High Polarization e- Gun : Optical Pumping of strained GaAs

Split degeneracy of  $P_{3/2}$   
& optical pumping between  $P_{3/2}$  and  $S_{1/2}$



theoretical



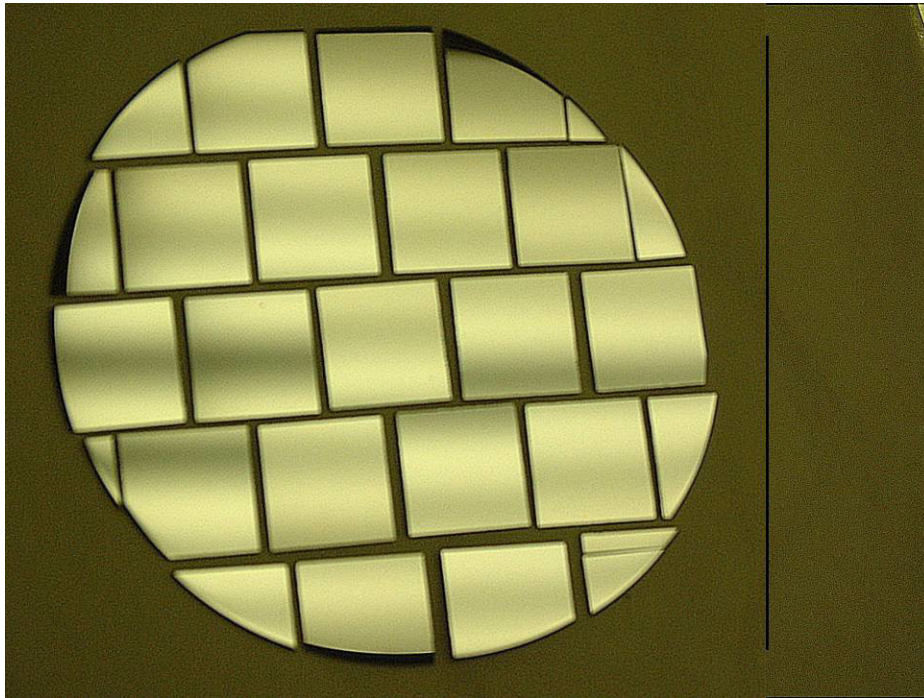
$P_e = +/- 100\%$ , with  $E_{\text{gap}} < E_{\gamma} < E_{\text{gap}+\delta}$

Experimentally  $\sim 85\%$

Slide is from : J. Grames, JLab, USA

# Photocathodes at Jlab, USA

3" wafer cleaved into square photocathodes (15.5 mm) for mounting on a "stalk" using In and Ta cup.



*3 " wafer cut into square photocathodes*

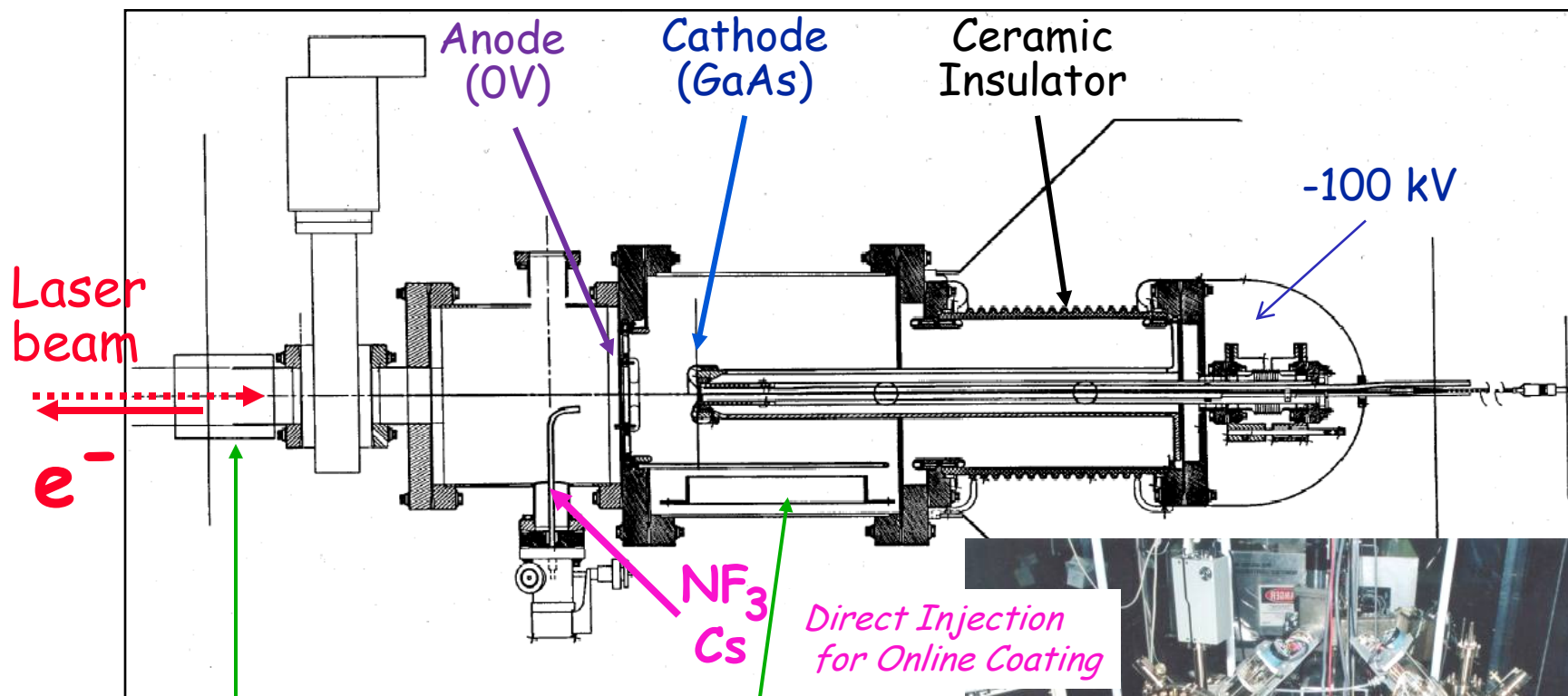


*Stalk for supporting 1 Photocathode*

*Slide is from : J. Grames, JLab, USA*



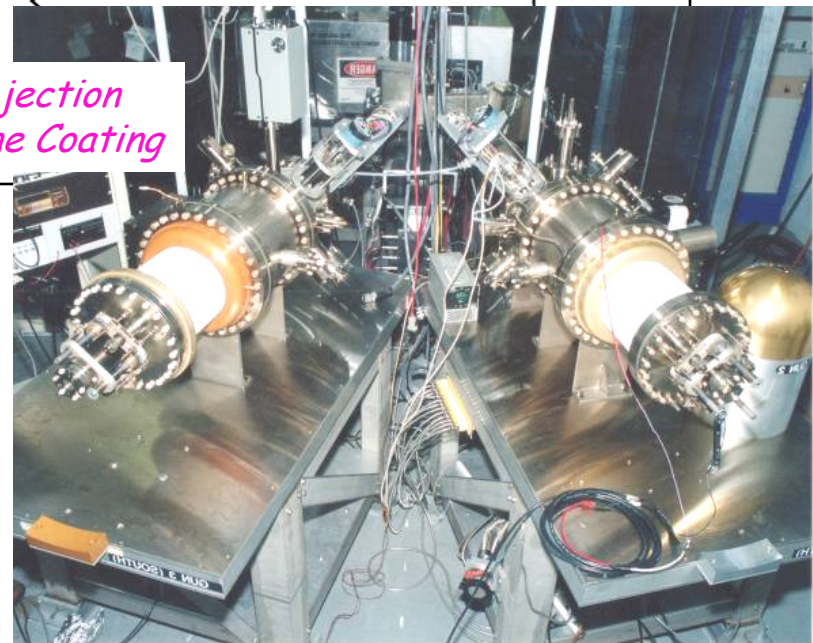
# Present JLab polarized gun design (USA)



NEG coated  
beampipe

Non evaporable getter pumps (NEG)  
4,000 liter/s pump speed  $\Rightarrow \sim 4 \cdot 10^{-12}$  mbar

*Mandatory to prevent Photocathode early aging*

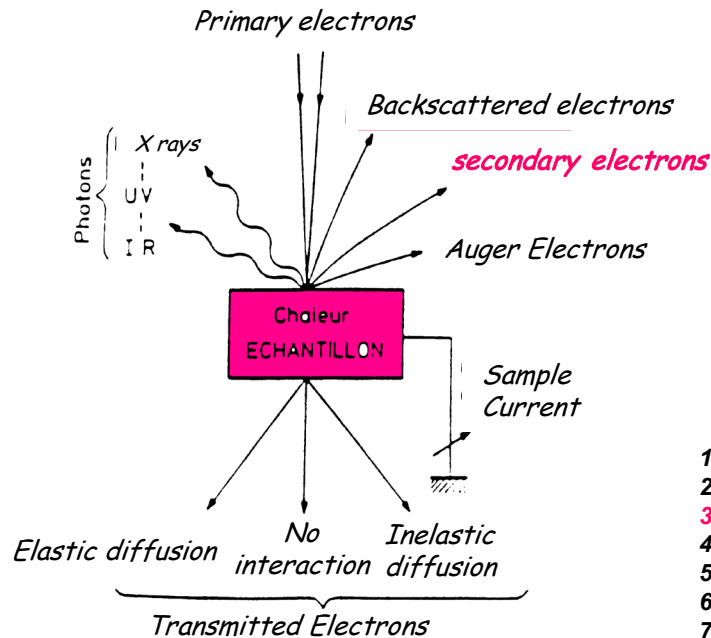


slide adapted from: J. Grames, JLab, USA

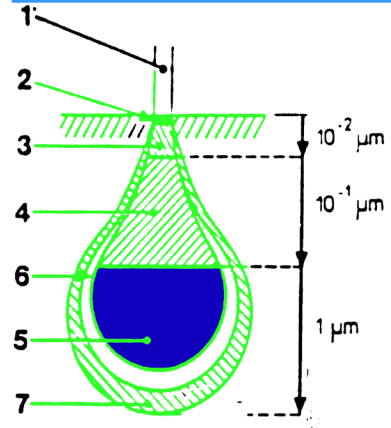
# Secondary Electron Emission

Emission of electrons from matter induced by impinging ionizing particles like :

- An incident electron
- An Ion
- A photon



Area of emission of specific Interactions in matter



- 1 Impinging electron
- 2 Auger electrons
- 3 Secondary electrons
- 4 Backscattered electrons
- 5 Characteristic X-rays
- 6 Continuous spectrum of X-rays
- 7 Fluorescence X rays

For a 40 keV incident electron beam

slide adapted from: J. Arianer



# Secondary Electron Emission Yield

Kinetic ejection condition

$$E_p > W_{\text{matter}}$$

SE Yield:

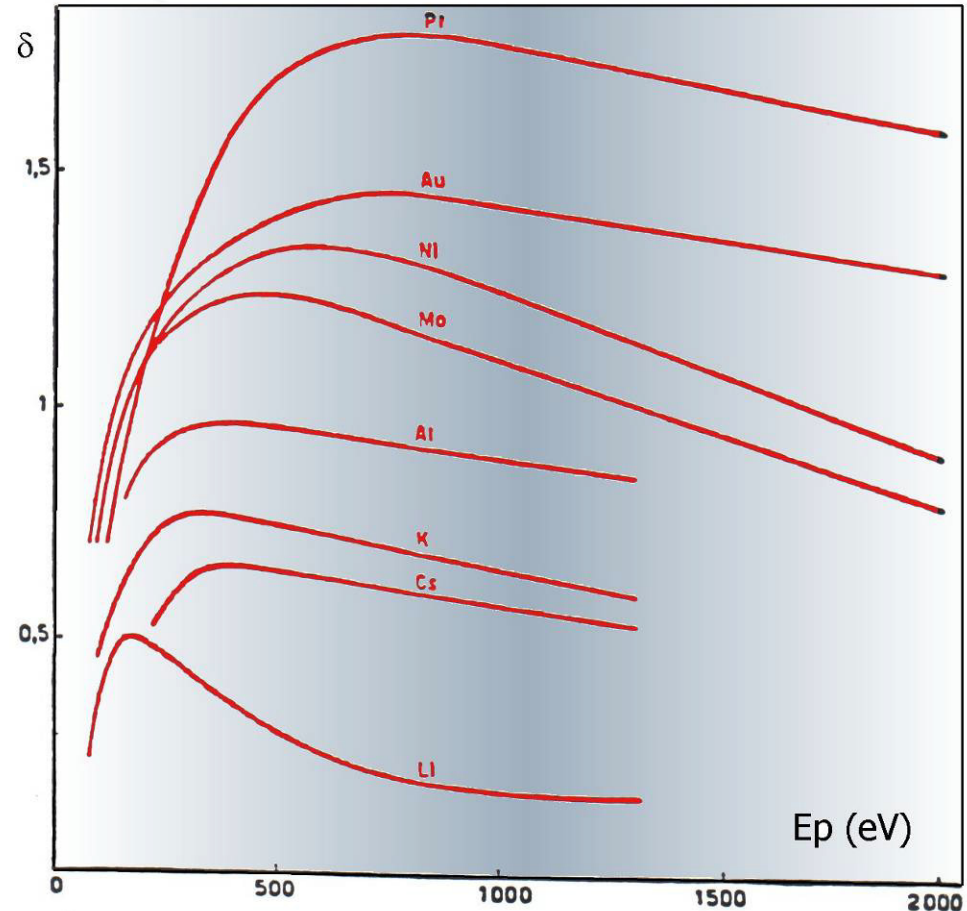
$$\delta = \frac{N_{e_s}}{N_{e_p}} \frac{\text{secondary}}{\text{primary}}$$

$\delta = f(E_p, \text{matter})$

0 ÷ some  $10^3$

likely

0 ÷ some 10

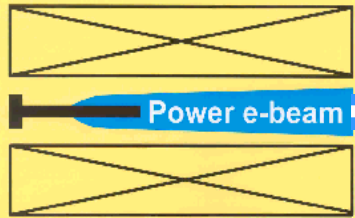


*=> Secondary Electron Emission can be used as an electron current amplifier*

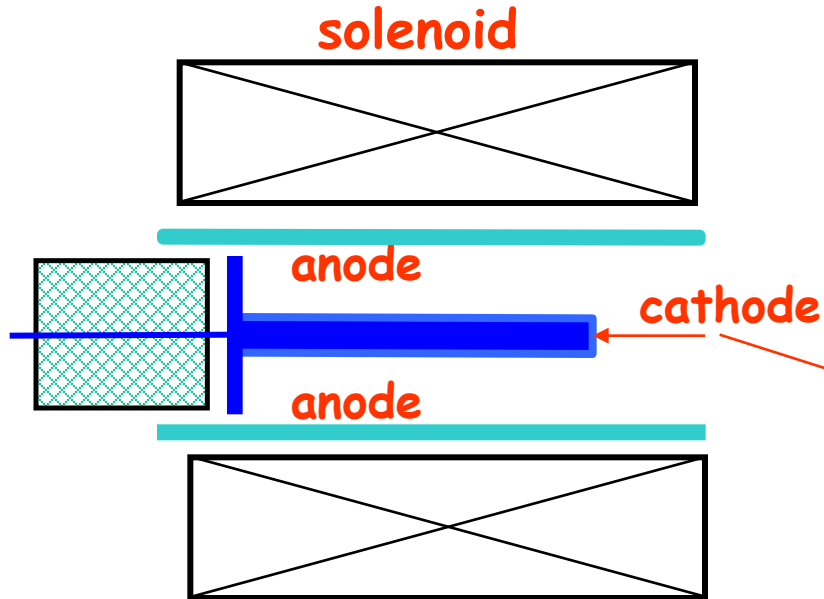
slide adapted from: J. Arianer

# SEMIG : Secondary Emission Magnetron Injection Gun

## SEMIG



Next 5 slides see: S.A.Cherenshchikov, A.N.Dovbnya, A.N.Opanasenko, National Science Center, Institute of Physics & Technology, Kharkiv, 310108 Ukraine.



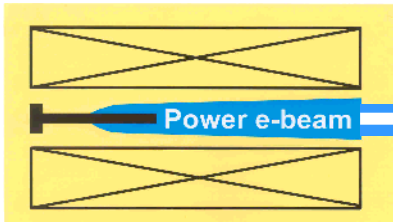
The schematic image of the gun



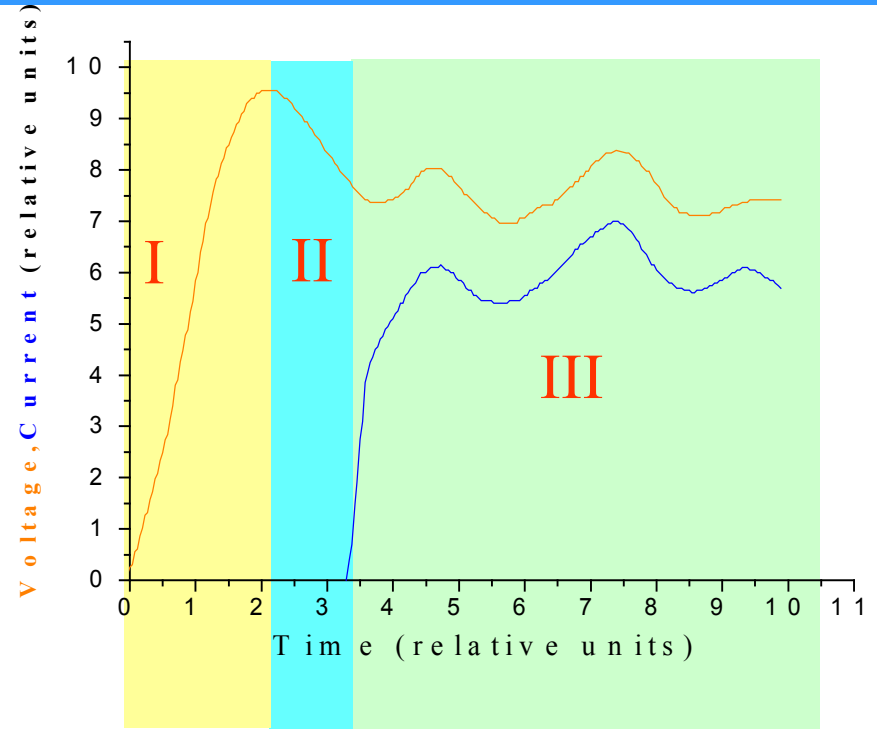
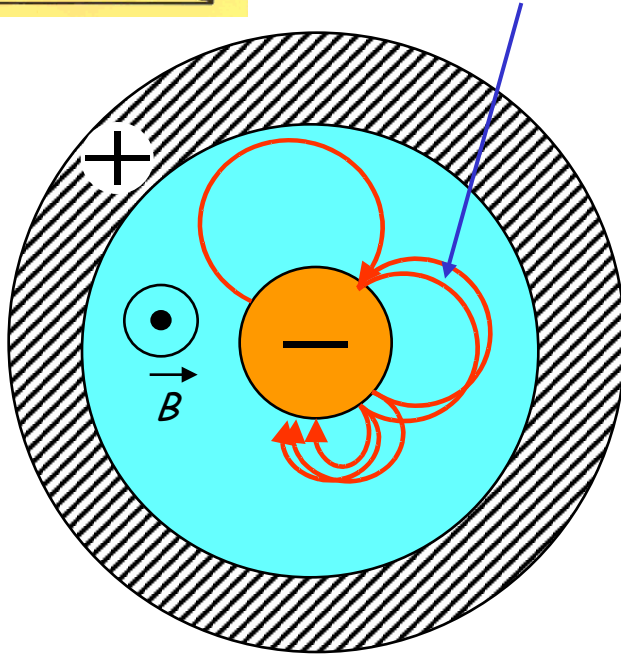
The set of cathodes

# SEMIG : Beam Ignition

## SEMIG



Electron trajectories



Secondary emission multiplication    Gun voltage and beam current dependence on time

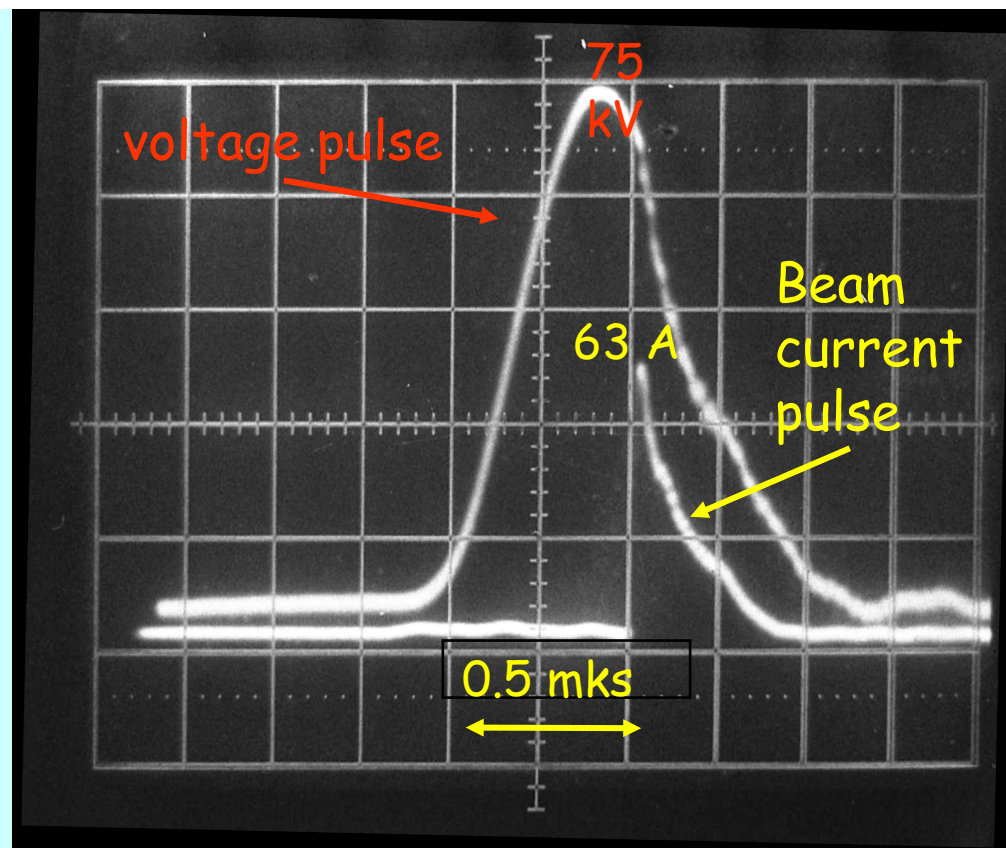
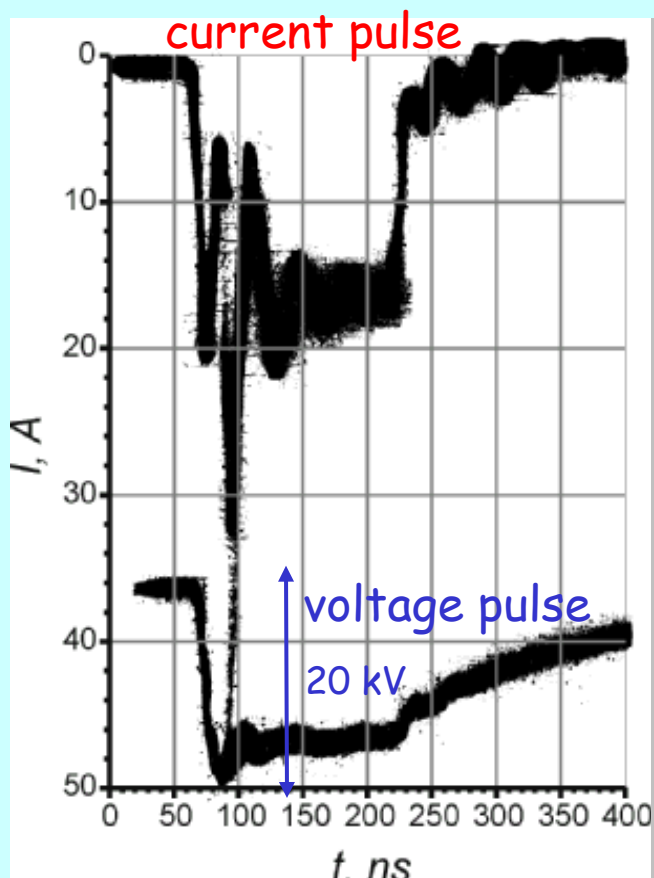
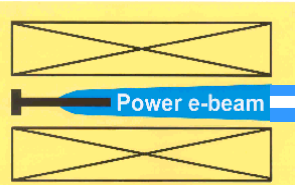
I. Voltage application ( $V=f(\text{time})$ )

II. Secondary emission multiplication

III. Self-support secondary emission

# SEMIG : electron pulses

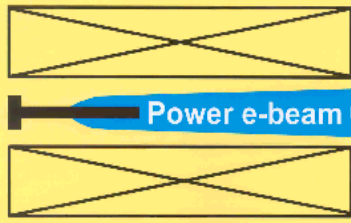
## SEMIG



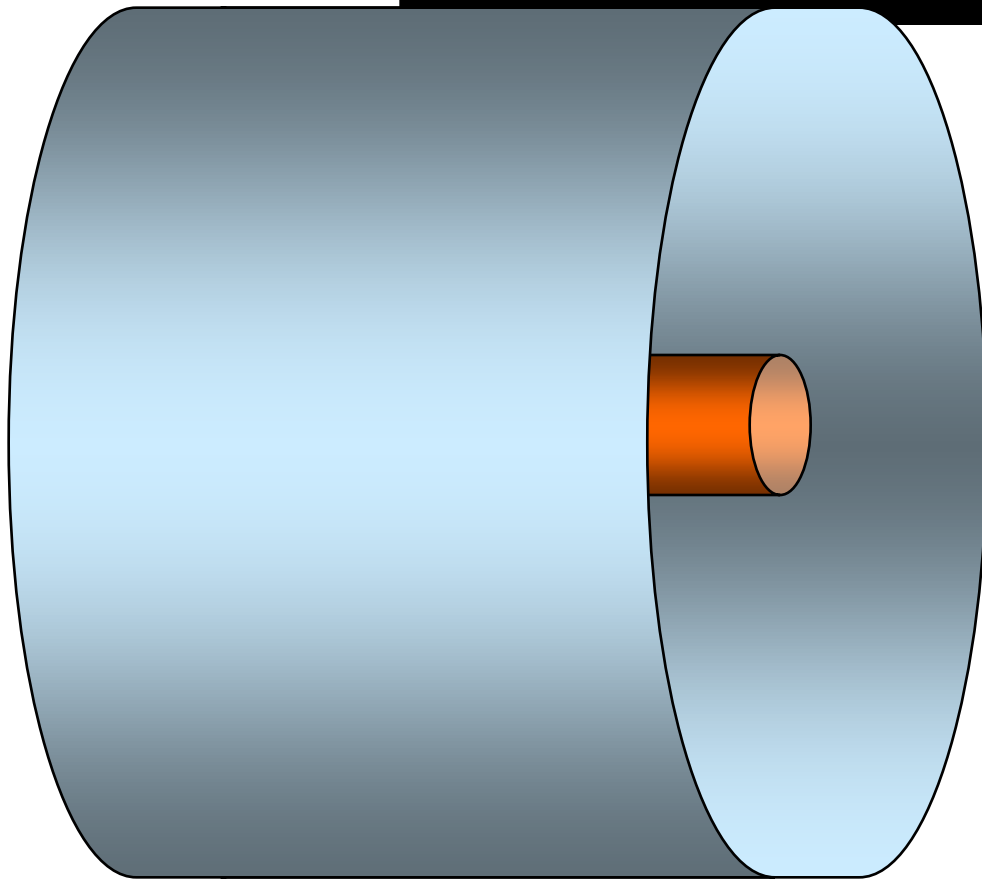
SEMIG ignition	Magnetic field 0.202 T
Cathode diameter	14 mm
Anode diameter	30 mm
Repetition frequency	3Hz

Cold-cathode magnetron ignition

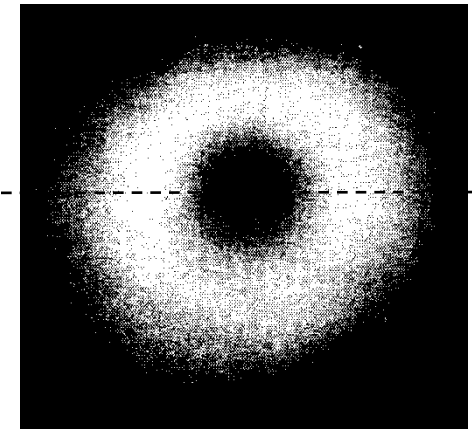
# SEMIG : beam size



## Beam Cross-Section in X-rays

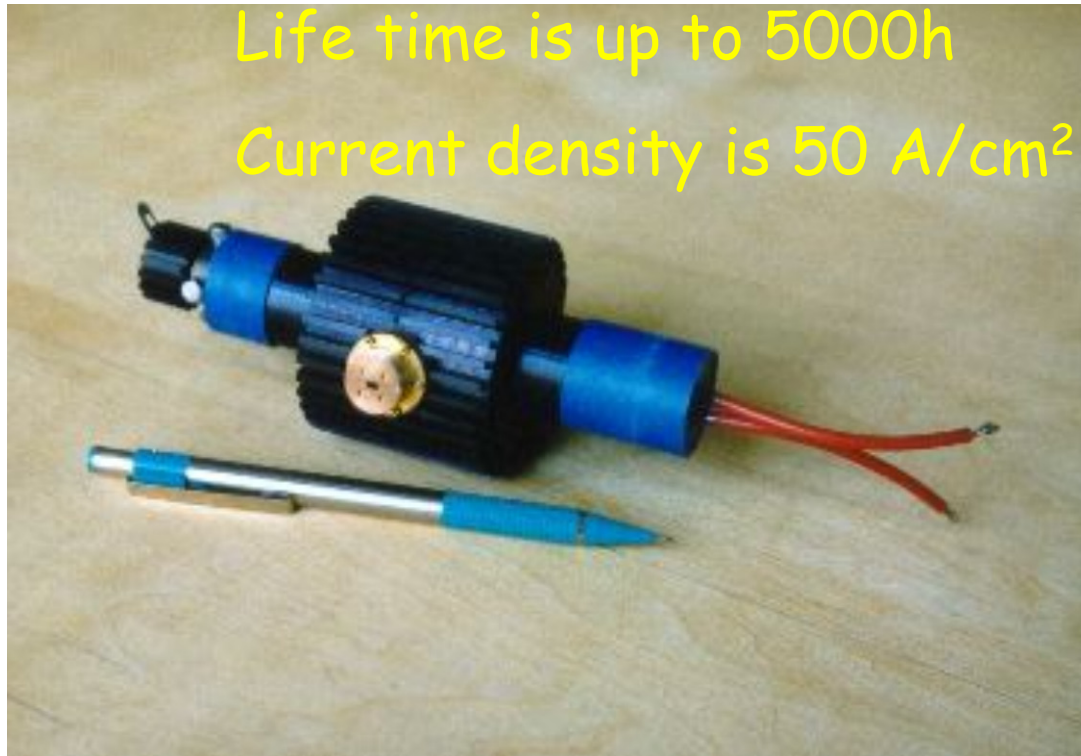
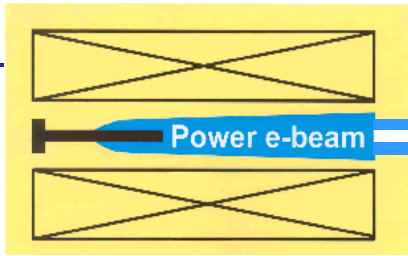


Gun end in scale



beam size  $D=1$  cm  
current  $I=10$  A,  
energy 40 keV.

# SEMIG : dimension **SEMIG**

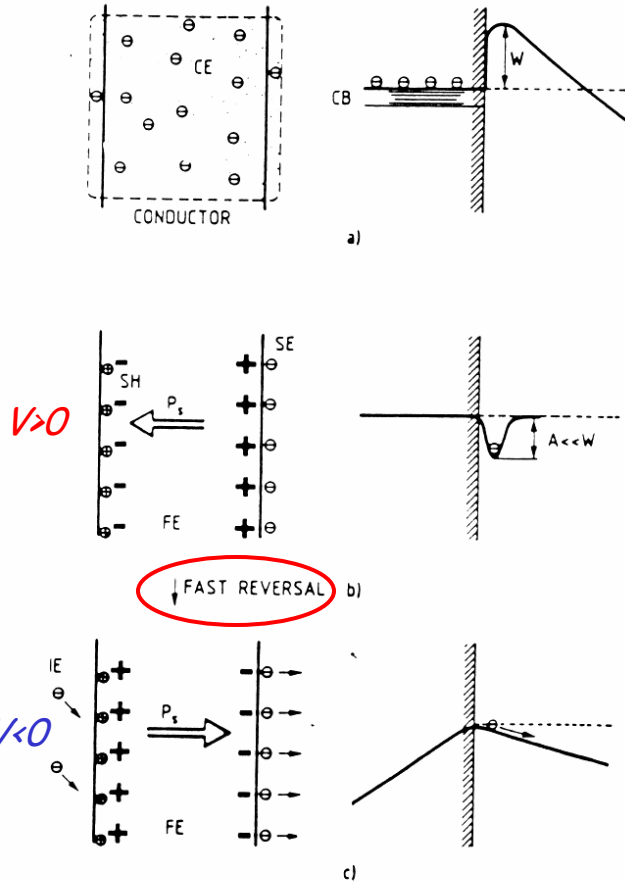


A secondary emission 3-mm magnetron with a platinum cathode

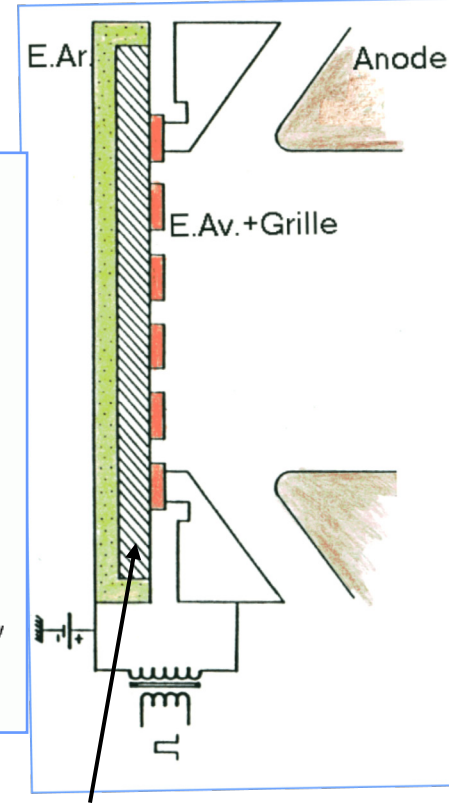
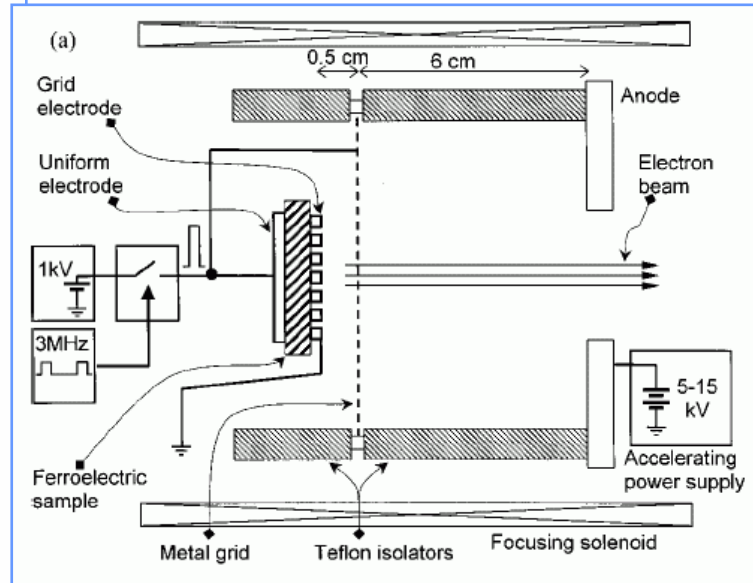


# Ferroelectric Emission

R&D in labs  
no contamination  
low cost, low vacuum  
simple Technology  
 $J > 100 \text{ A.cm}^{-2}$



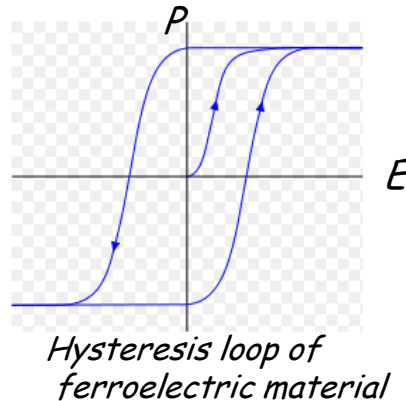
Principle of FE space-charge emission after a polarization change. a) Emission of conduction electrons from a metal ( $W$  = work function,  $CB$  = conduction band). b) Neutralization of FE by screening electrons (SE) and holes (SH). c) Emission from FE after  $P_s$  reversal and neutralization by injected electrons (IE).



Pb,La,Zr,Ti (PZLT)

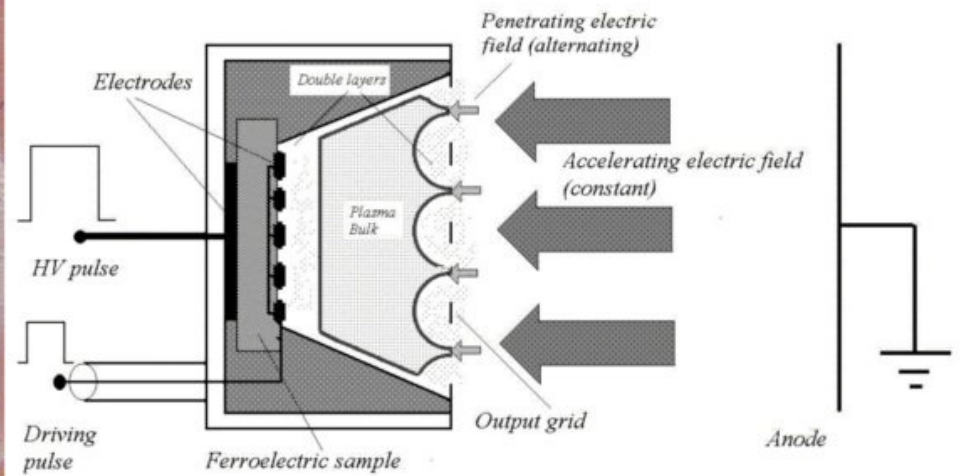
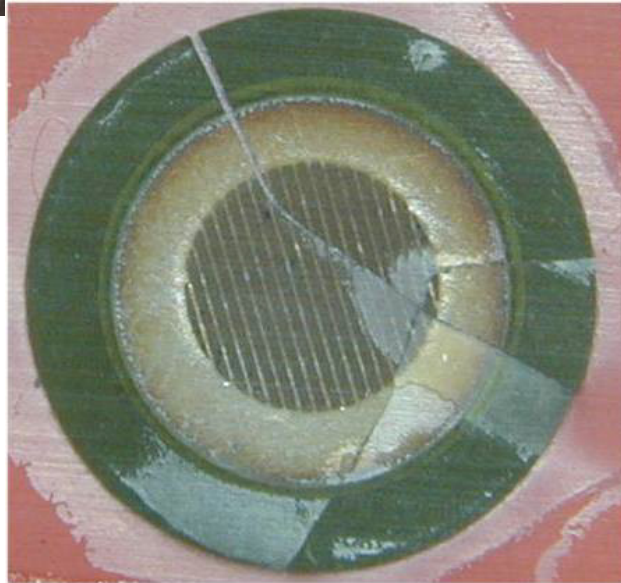
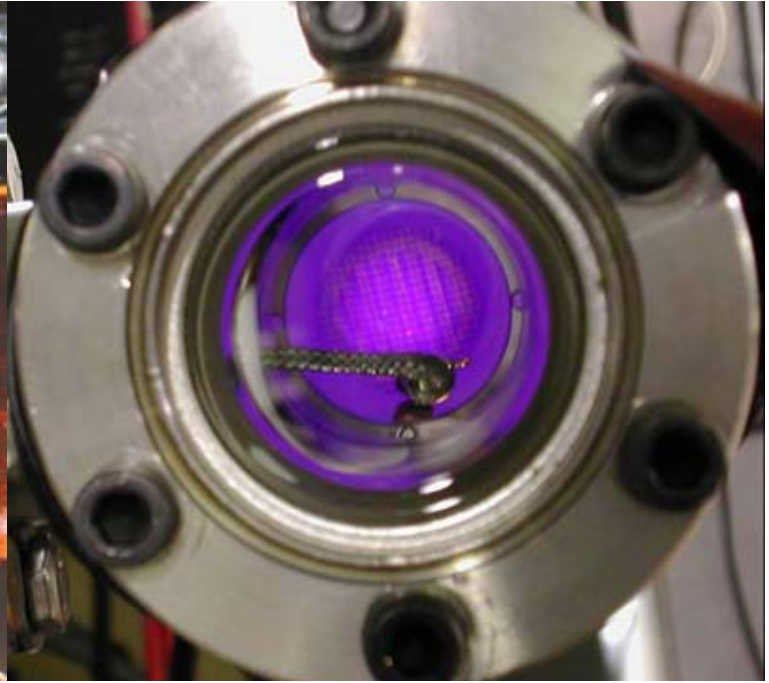
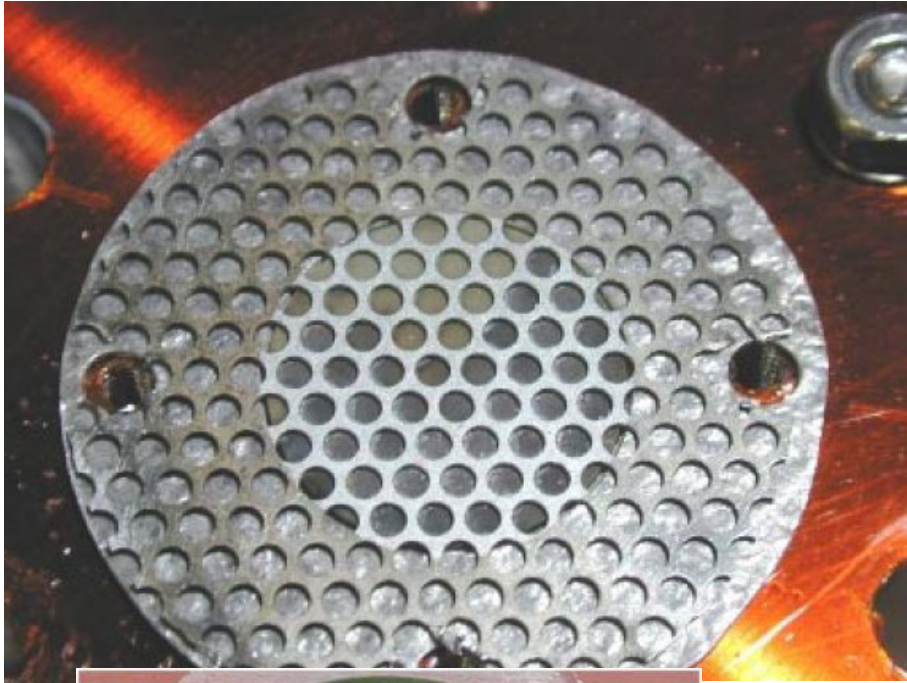
Ceramic coated on both face  
With thin metal layer

Behaviour and theory  
still under study!





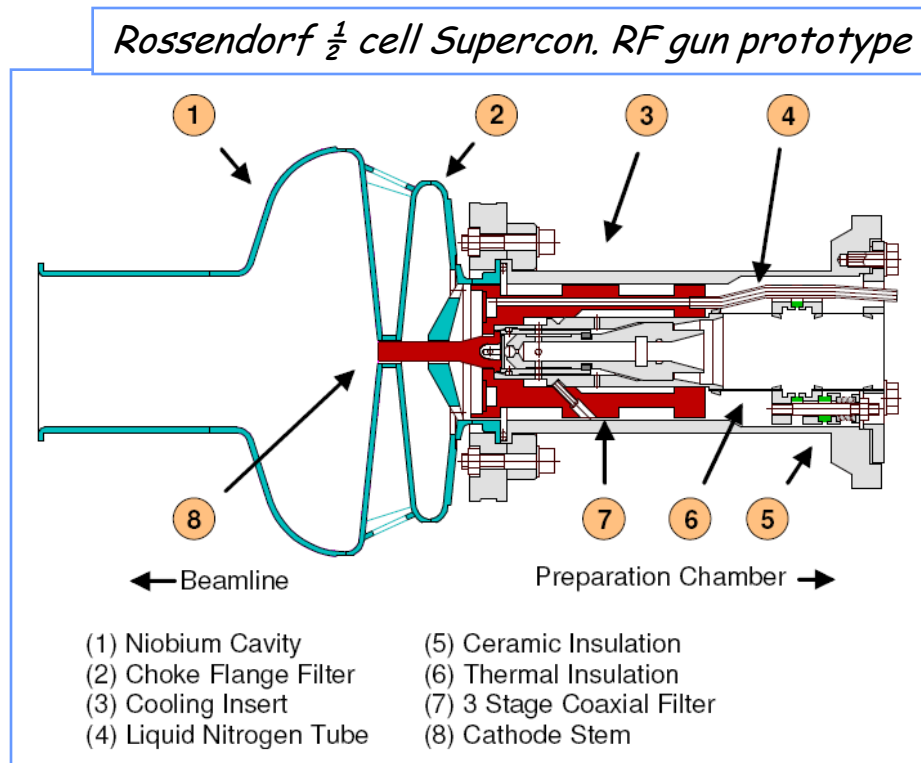
# FerroElectric Emission GUN



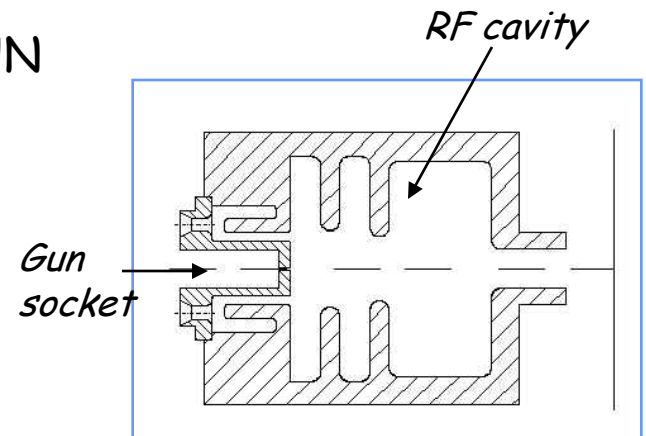
# Radio Frequency Guns

## The electron Gun is directly coupled to a RF Cavity

- compact solution to accelerate directly above MeV Energies
- higher currents are reachabme
- Can be used with many kind of electron GUN



*D.Janssen et al., NIM A507(2003)314.*

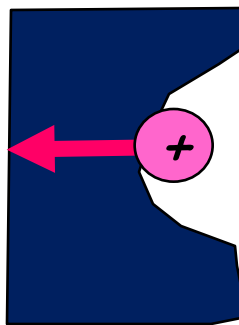
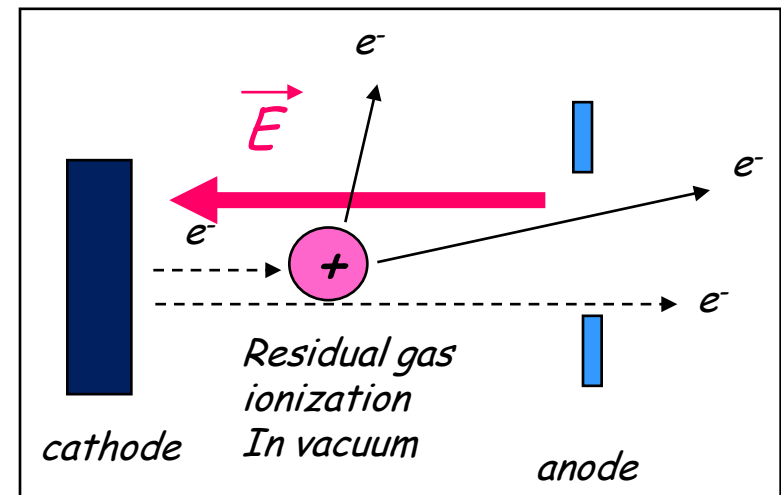
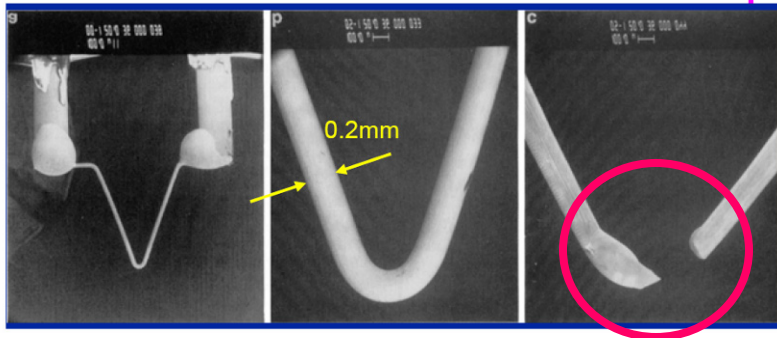


*A 3 GHz thermionic RF gun has been designed. It will produce a 2.3 MeV electron beam with bunch charge up to 0.2 nC (600 mA) at 10 pmm mRad normalised emittance.*



# Aging of cathodes by Sputtering Effect

- The electron beam ionizes partially the residual gas under vacuum
- The negative biased voltage of the gun cathode accelerates ions toward its surface
- The ion bombardement sputters atoms from the lattice and dig holes
- Sputtering is also preseted in Ion Source course



*Cathode bombardment :  
Atoms are expelled out the lattice*

